



Science & Technology Facilities Council

Technology

532. Wilhelm and Else Heraeus-Seminar
High-Resolution Pixel Detectors and their Use in
Science and Society
23-25 May 2013, Bad Honnef

CMOS Image Sensors at the Rutherford Appleton Laboratory

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on behalf of the CMOS Sensor Design Group

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Oxfordshire, UK

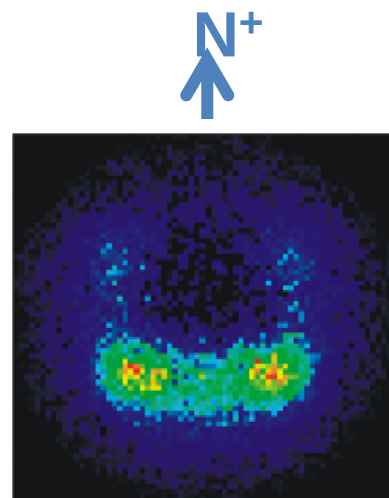
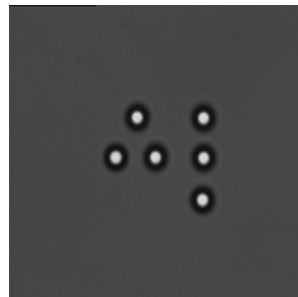
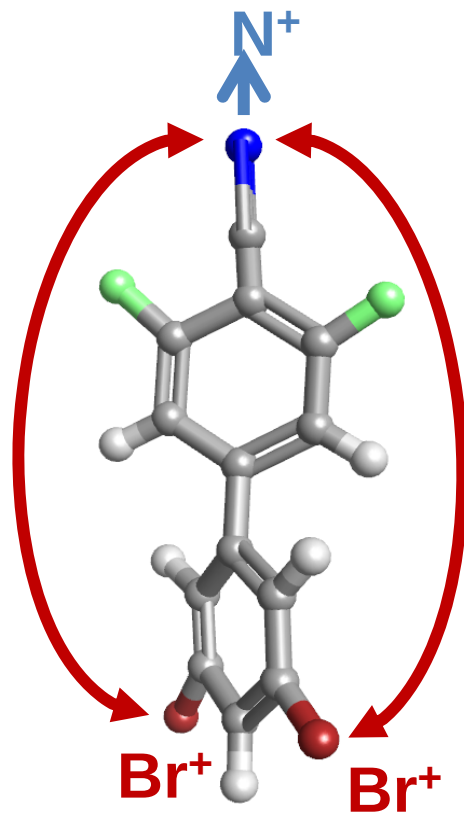
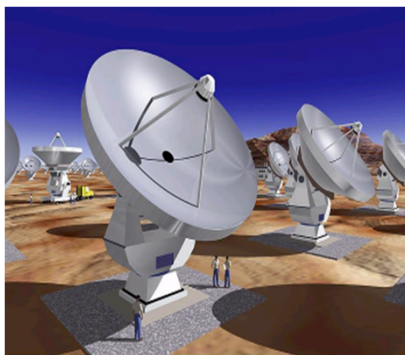
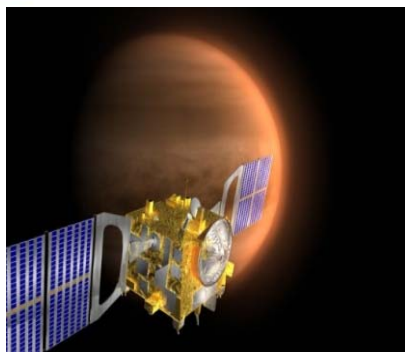
E-mail: renato.turchetta@stfc.ac.uk



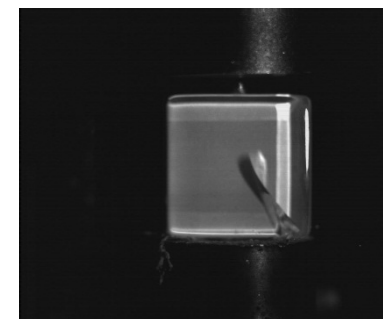
- **Introduction**
 - **Large area CMOS image sensor**
 - **Ultra-high speed CMOS image sensors**
 - **Conclusion**
-



CMOS Image Sensor at RAL



Br^+





Science requirements

Low noise

High Dynamic
Range (HDR)

Radiation
hardness

High speed

High
Quantum
Efficiency

Low power

Large data
volume

Large area
sensor

...

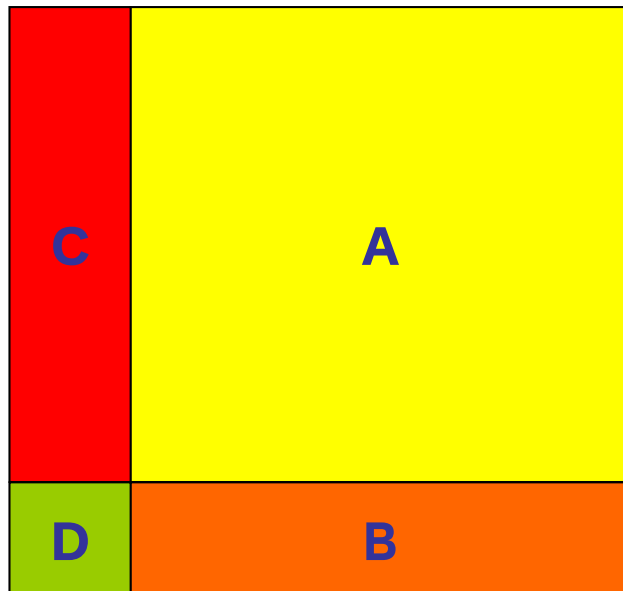
Lossless
compression



Large area sensor. Stitching.

Reticle size is just over 2cm x 2cm → 'stitching'

Reticle is subdivided in blocks

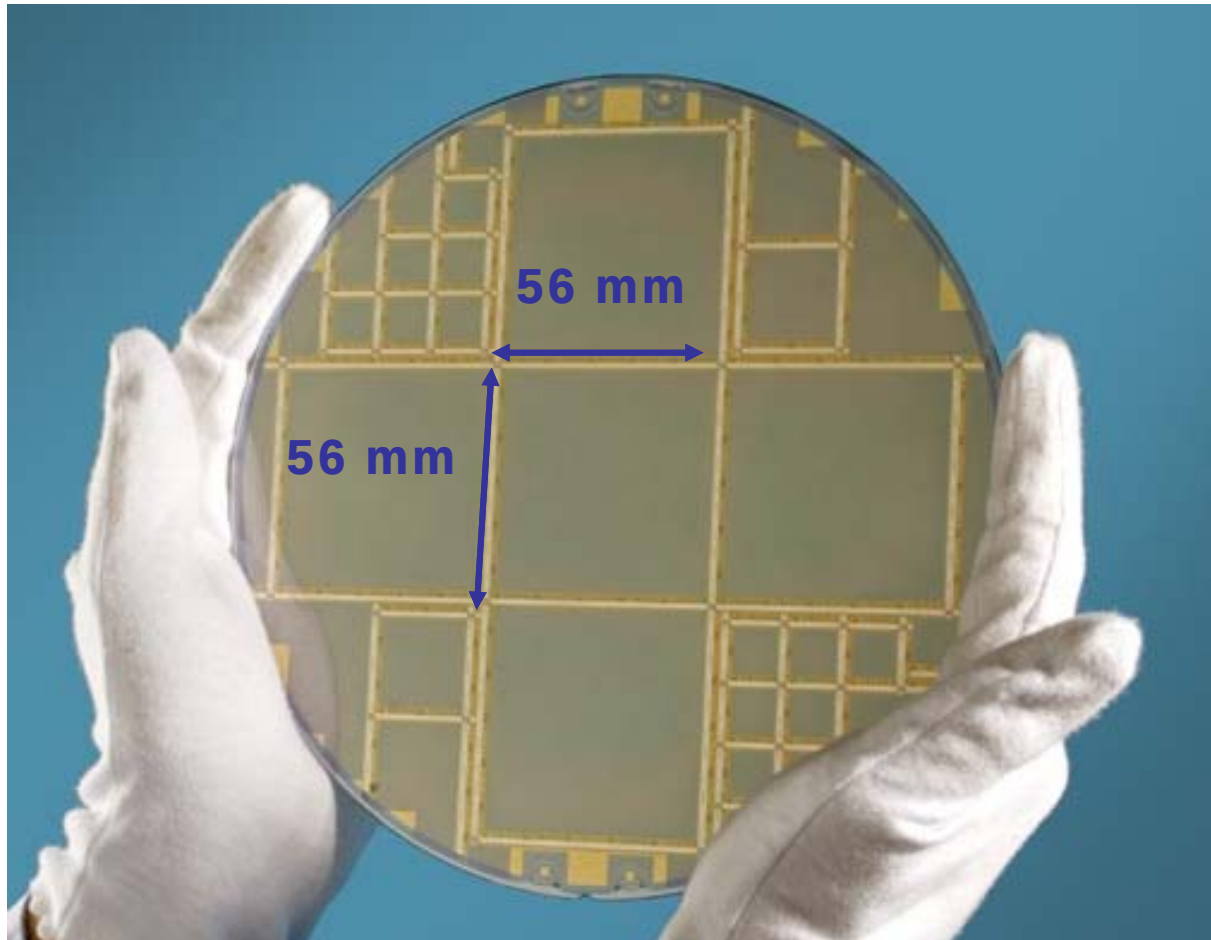


Sensor size freed from
reticle limitation → up
to single sensor per
wafer

Sensors of different
sizes can be
manufactured



Large area sensor. Stitching.

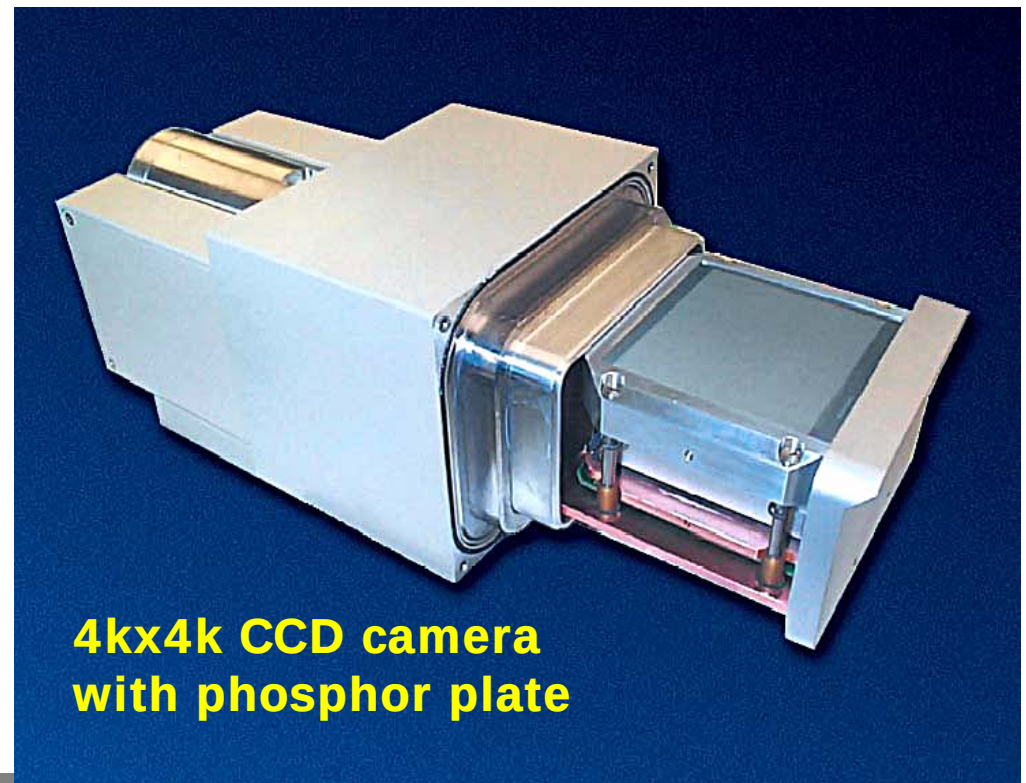
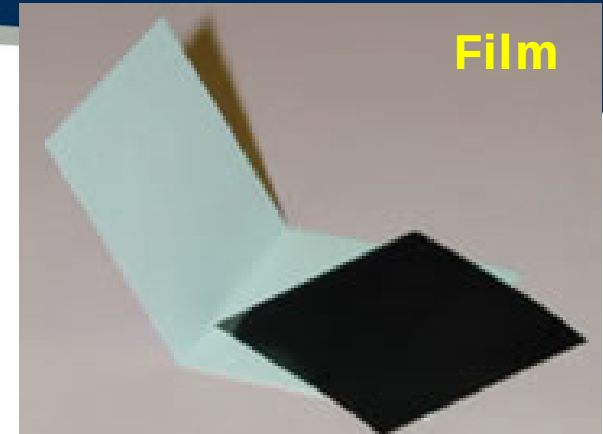




Transmission Electron Microscopy (TEM). Prior art.

➤ Film: direct detection, very good resolution, non digital, poor S/N for weak exposure

➤ CCD with phosphor: indirect detection (radiation hardness), phosphor ruins spatial resolution, good for tomography



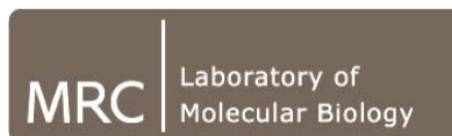
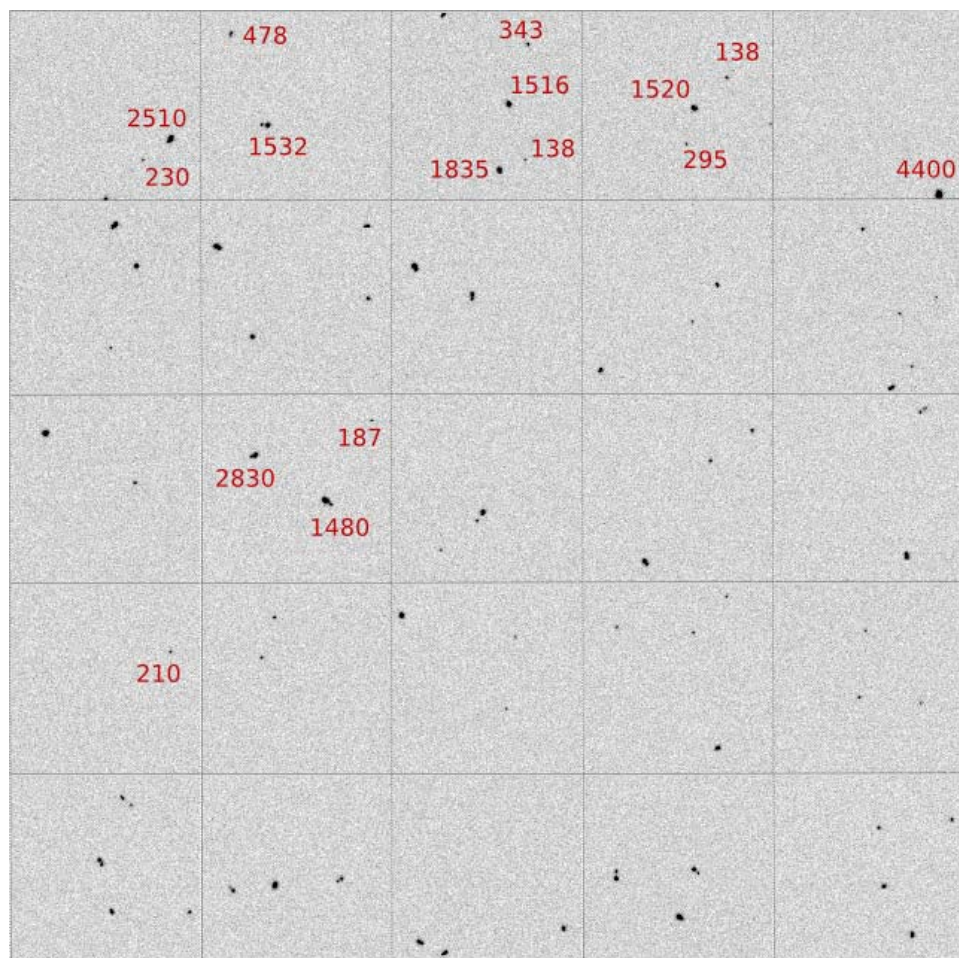


CMOS Sensor for TEM

- Direct detection
 - Good single electron sensitivity
 - Good MTF and DQE
 - Radiation resistant
 - 4Kx4K array
 - 16 million pixels
-



Detection of electrons in CMOS



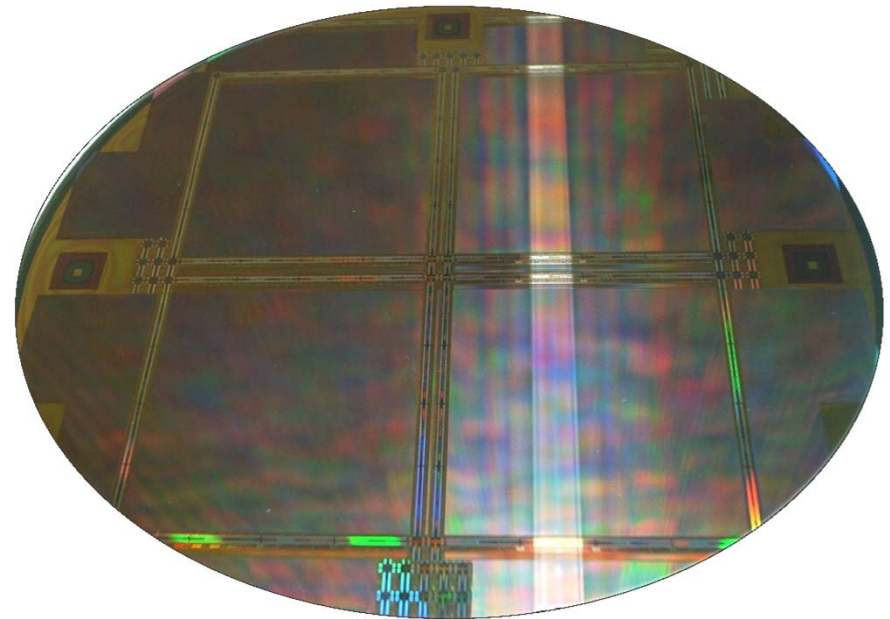
MAX-PLANCK-GESELLSCHAFT





A 16Mpixel sensor for TEM

- 61x63 mm² silicon area (4 dies per wafer)
- 0.35μm CMOS
- 16 million pixels, 4Kx4K array
- 14 μm pixels
- 32 analogue outputs
- 40 fps
- Pixel binning 1X, 2X and 4X
- ROI readout
- 83 e- rms noise
- Full well 120ke-
- Radiation hardness of >500 million of primary electrons/pixel (>20 Mrad)
- 20% QE for visible light





Wafer-scale sensor for X-ray medical imaging

Motivations

- Extra-oral dental
- with tiling:
 - Mammography
 - Chest imaging
 - Security
 - ...

Guidelines

- Wafer-scale sensor
- One sensor per 200 mm wafer
- 3-side buttable → 2xN tiling
- Radiation hard design
- Design for yield



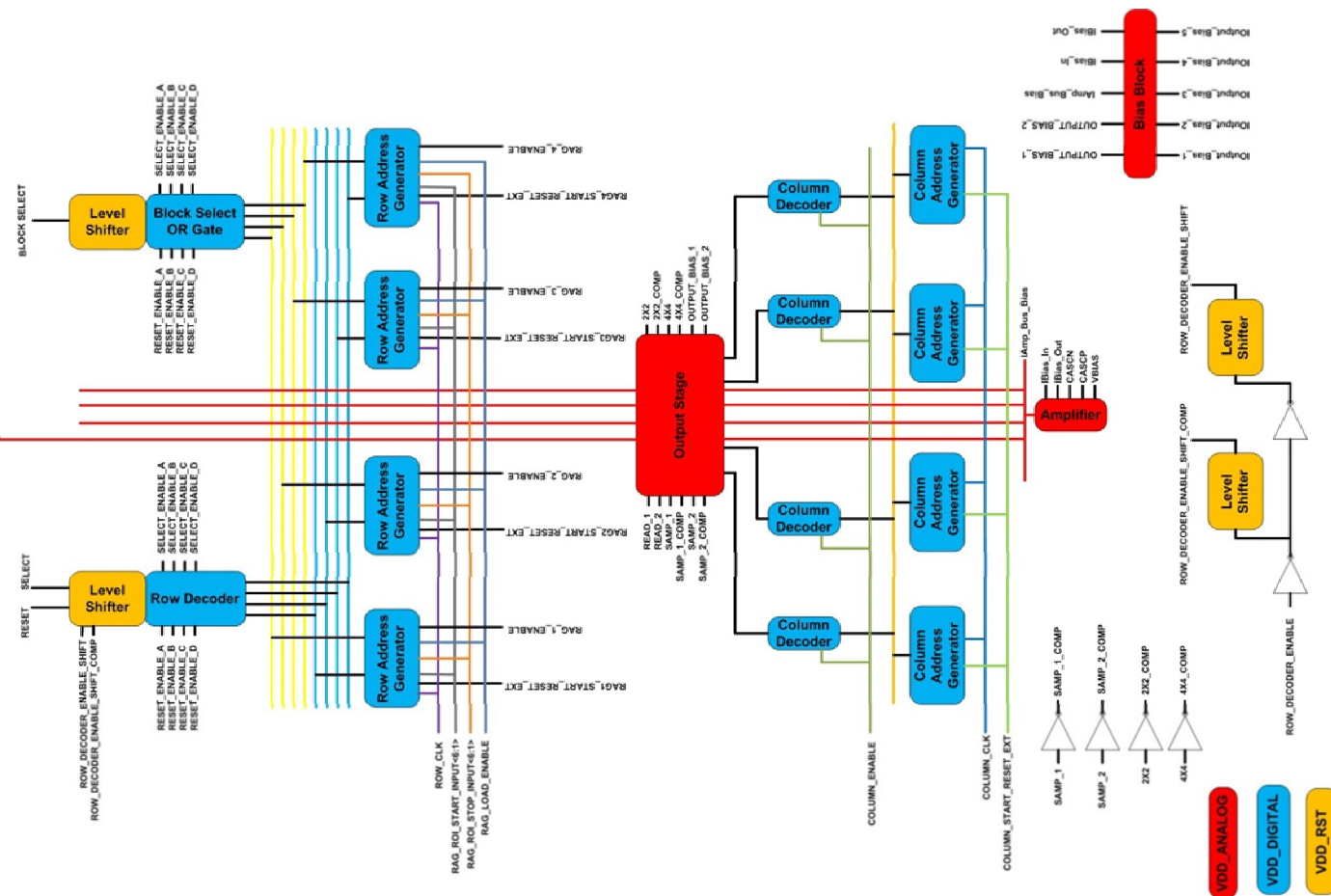
Lassena. Floorplan

To the pixel:

3T pixel base with

Low noise,
large partially
pinned diode

Binning
capability

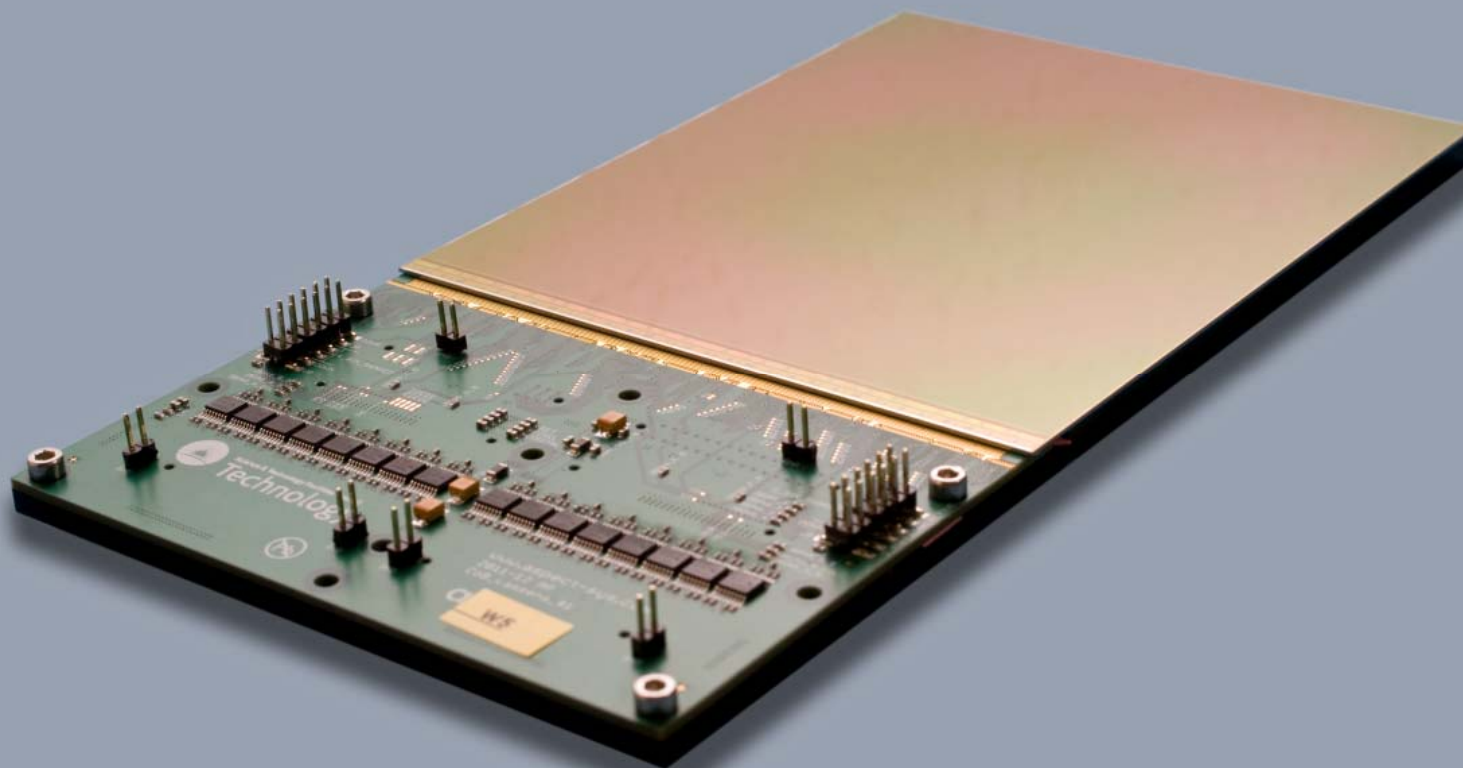




- High resolution. 50 μm pixel.
 - High-speed. Over 30 frames per second at full resolution.
 - Low noise. 68 e- rms in full frame to give very high sensitivity.
 - Large area coverage. The sensor is 3-side buttable so that tiled sensors can cover any length of an area 28 cm wide.
 - High dynamic range. Multiple programmable integration times
 - Binning x2, x4
 - ROI readout
-



Lassena. A 6.7Mpixel, wafer-scale sensor





Optical parameters

Optical performance			
Rms electronic noise	e- rms	68	Full resolution mode (i.e. no binning)
		335	Bin 2x2 mode
		608	Bin 4x4 mode
Linear full well	e-	112,000	Full resolution mode (i.e. no binning)
		1,253,000	Bin 2x2 mode
		5,012,000	Bin 4x4 mode
Maximum full well	e-	144,000	Full resolution mode (i.e. no binning)
		1,374,000	Bin 2x2 mode
		5,496,000	Bin 4x4 mode
Dynamic range (Linear)	bits	10.7	Full resolution mode (i.e. no binning)
		11.9	Bin 2x2 mode
		13.0	Bin 4x4 mode
Dynamic range (Maximum)	bits	11.0	Full resolution mode (i.e. no binning)
		12.0	Bin 2x2 mode
		13.1	Bin 4x4 mode
Readout speed	frames per second	35	Full resolution mode (i.e. no binning)
		70	Bin 2x2 mode
		140	Bin 4x4 mode
Quantum efficiency	Measured @ 540nm	50%	
Lag		Negligible	
Other			
Power supply	V	3.3	
Number of pads	480	All on one side	
Power Consumption (mW)	W	<2.5	CMOS only



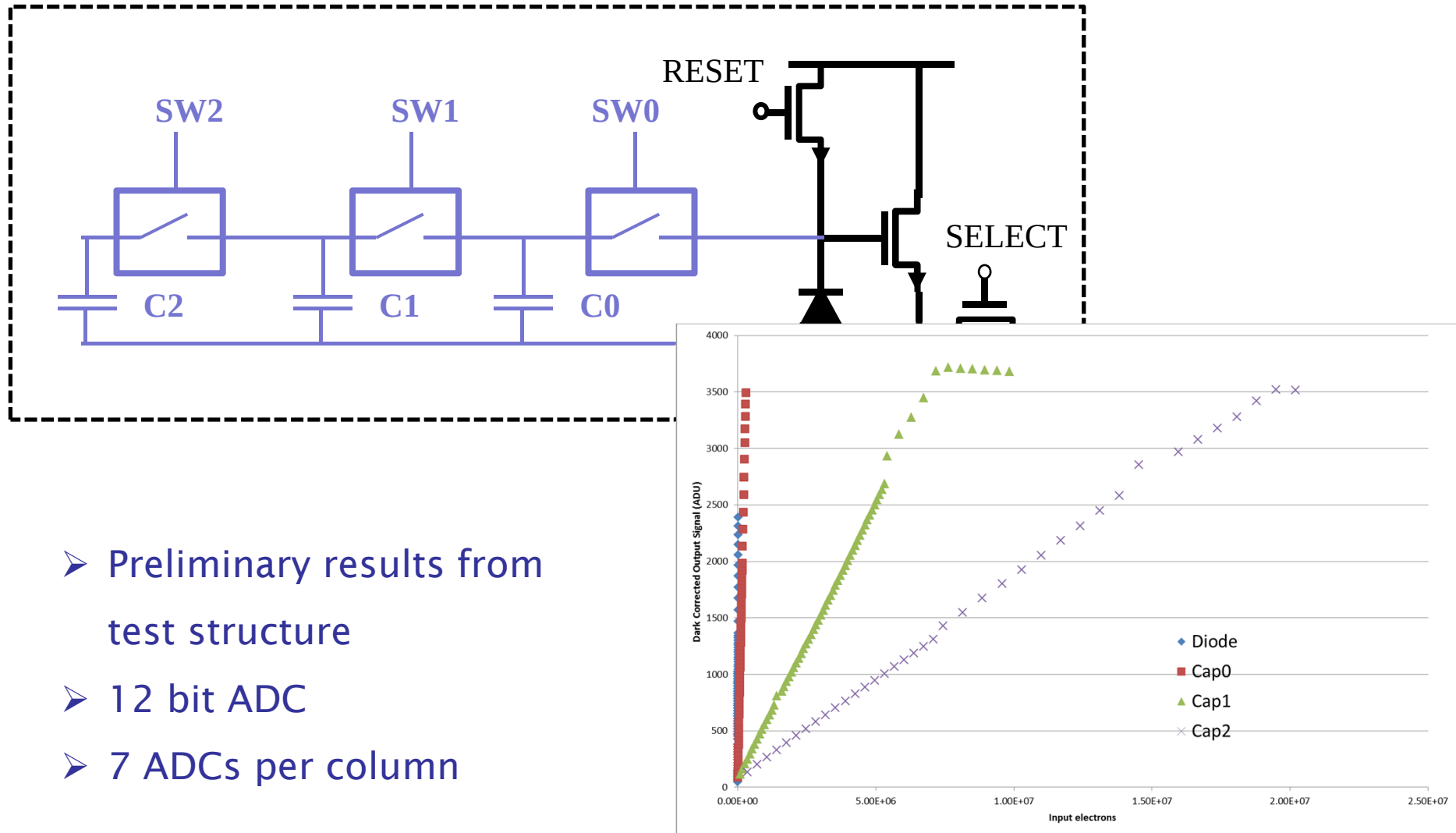
Pixelated Energy Resolving CMOS Imager, Versatile and Large





Percival target specifications

- Low energy X-ray detection $< \sim 2,000$ eV
 - High efficiency $\rightarrow$ back-side illuminated and direct detection
 - High resolution $\rightarrow$ 4kx4k on a $25\mu\text{m}$ pitch
 - Good single photon sensitivity $\rightarrow$ low noise
 - High dynamic range, i.e. up to $\sim 2 \times 10^5$ photons @ 250 eV $\rightarrow$ high dynamic range (HDR) pixel $\rightarrow \sim 120\text{dB}$ or full well > 10 Me-
 - High frame rate $\rightarrow$ 120 fps
 - Fully digital
-





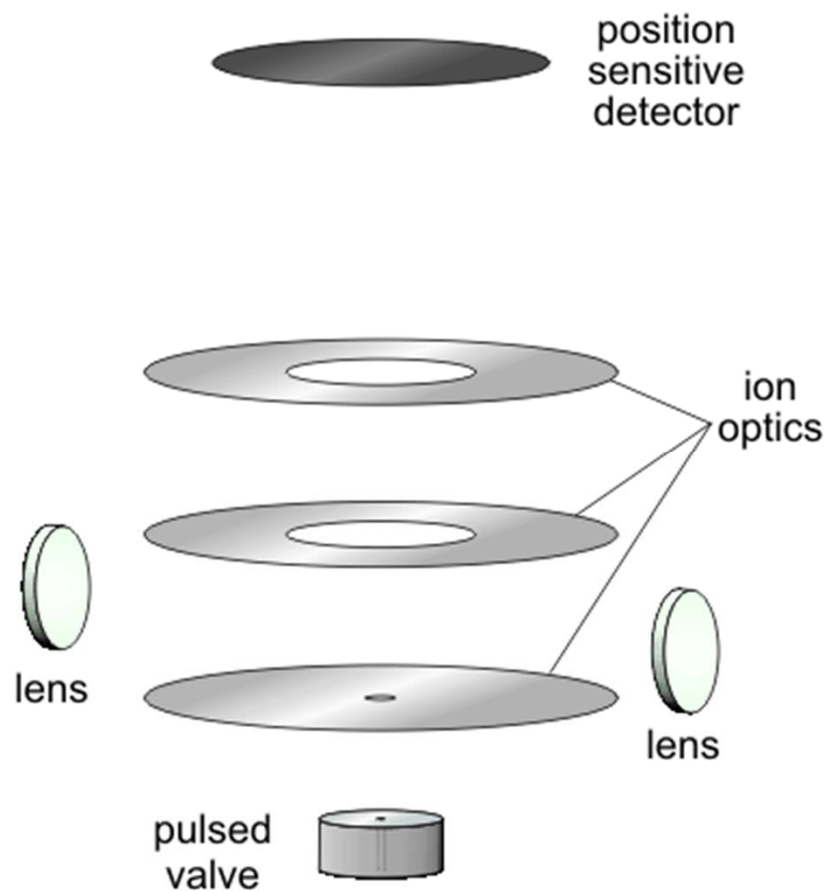
Percival sensor floorplan

- 16 MPix resolution
- 120 fps (digital CDS)
- High dynamic range (4 gains per pixel)
- 12+1 bit ADC
- 15 bits per pixel (2 gain bits + 13 bits)
- Digital I/O (LVDS)
- 60 Gbit/sec continuous data rate





Time-Of-Flight Mass Spectroscopy

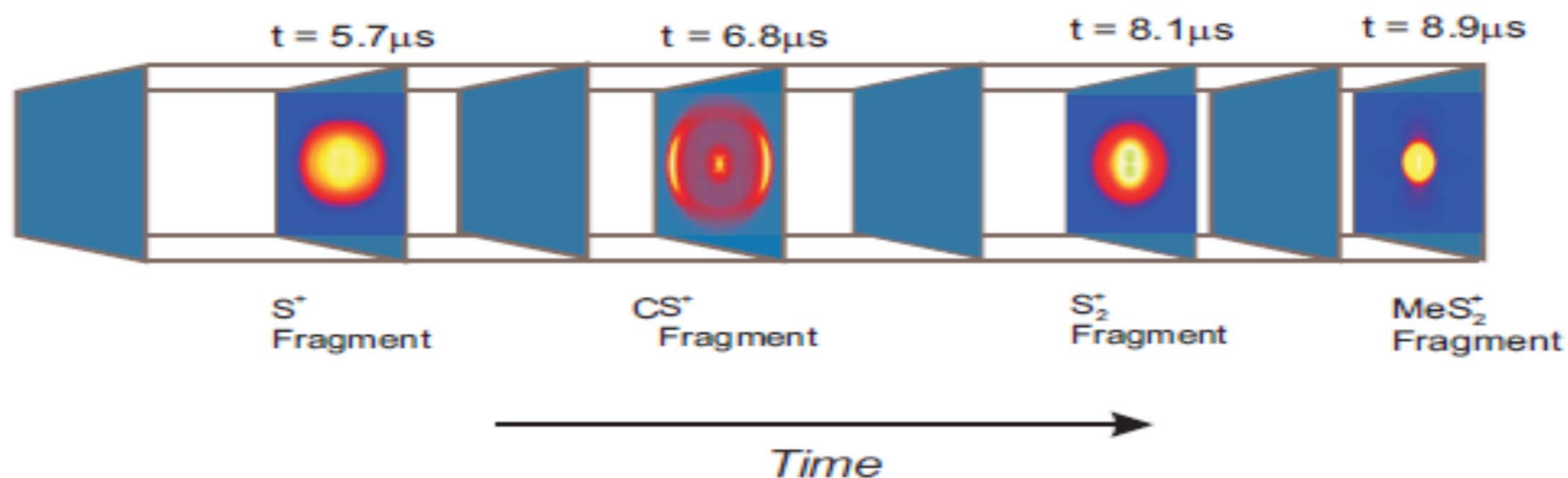


Requirements

- Spatial information
- Timing information



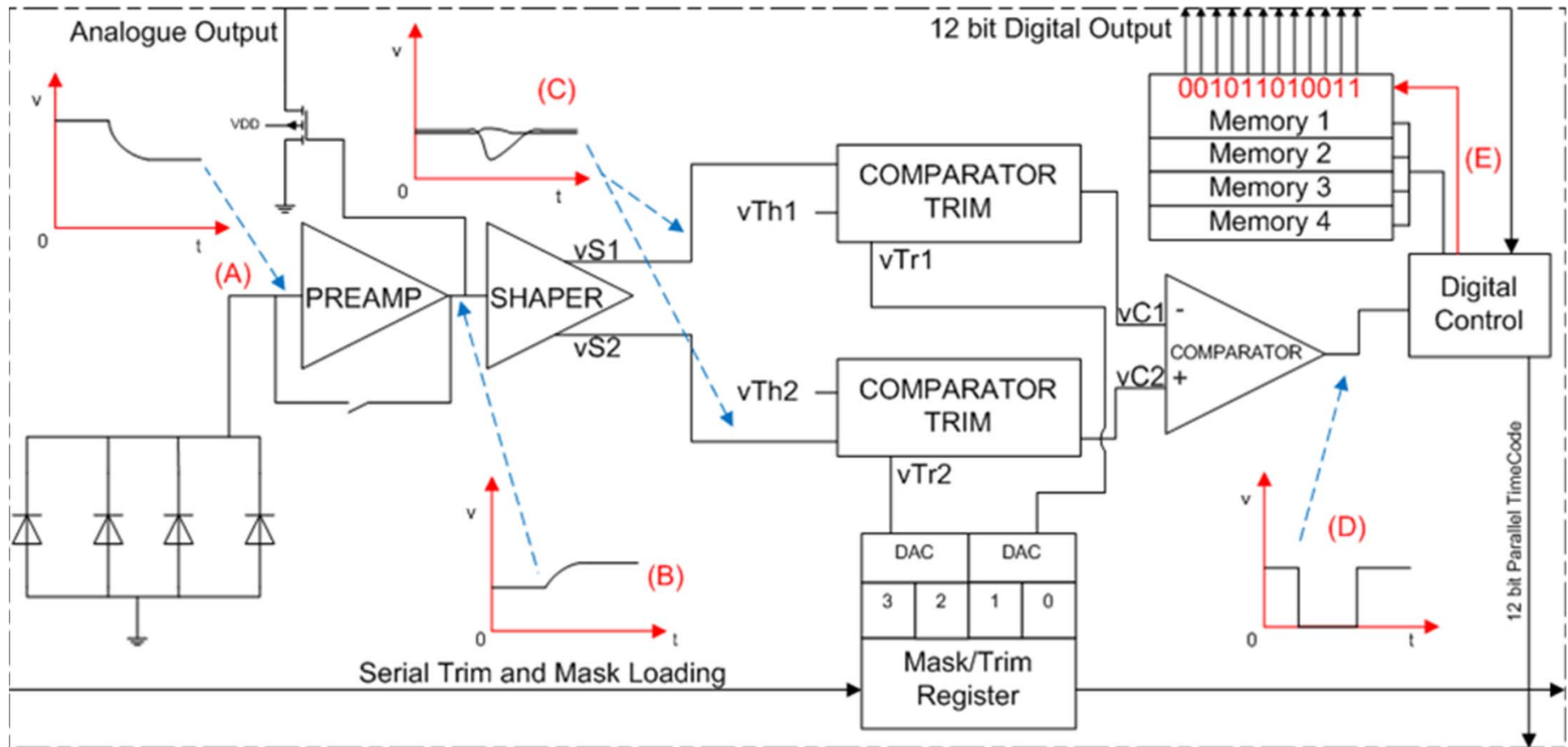
Time-Of-Flight Mass Spectroscopy





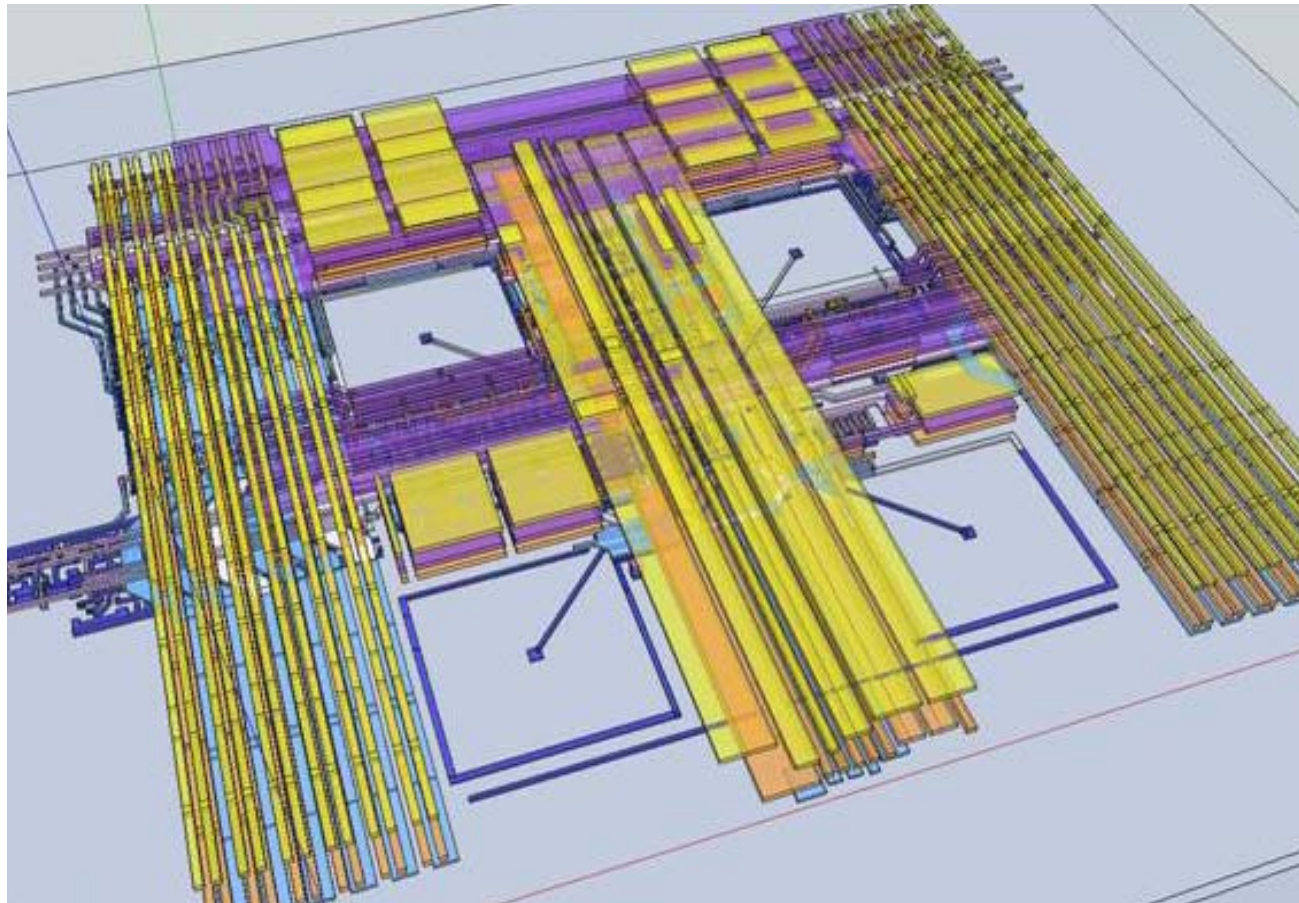
PIImMS. A single particle CMOS Image Sensor.

PIImMS – Pixel Imaging Mass Spectrometry





PImMS pixel layout



Over 600

transistors

Modified process

developed with

TowerJazz: deep P-

implant for 100%

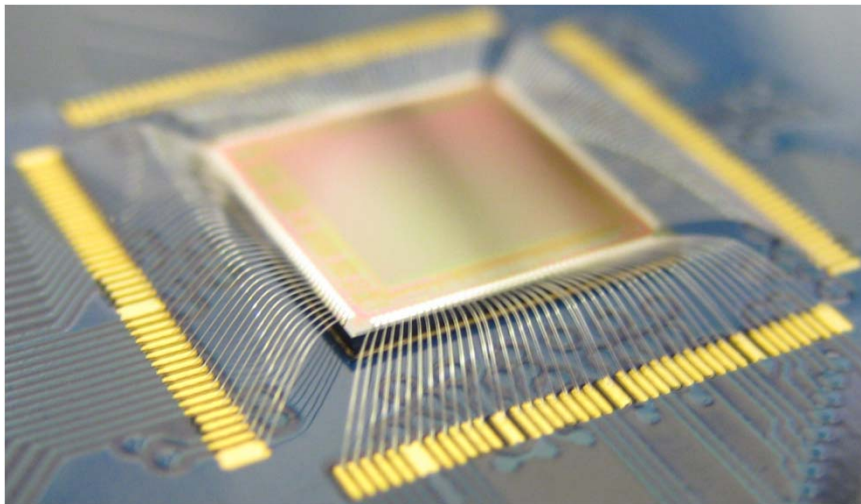
fill factor and true

CMOS



PIImMS1

72 by 72 pixel array



$\sim 2 \times 10^{11}$ pixel/sec

PIImMS2

324 by 324 pixel array
70 μm x 70 μm pixel size

Time-code resolution
= 25 ns (12.5 demonstrated already
on PIImMS1)

4 event stored in each pixel

12 bit time-code resolution

Analogue readout of intensity
information

Equivalent pixel rate for standard full
frame camera

$\sim 4 \times 10^{12}$ pixel/sec



Target specifications

- Ultra-high speed (>1 MHz) with high frame depth (~ 200 cells)
 - High resolution ($\sim$ Megapixel)
 - High-speed ($\sim$ kfps) for continuous readout
 - 10 bit resolution
 - Flexible trigger (pre/post/center)
 - 35mm format
-



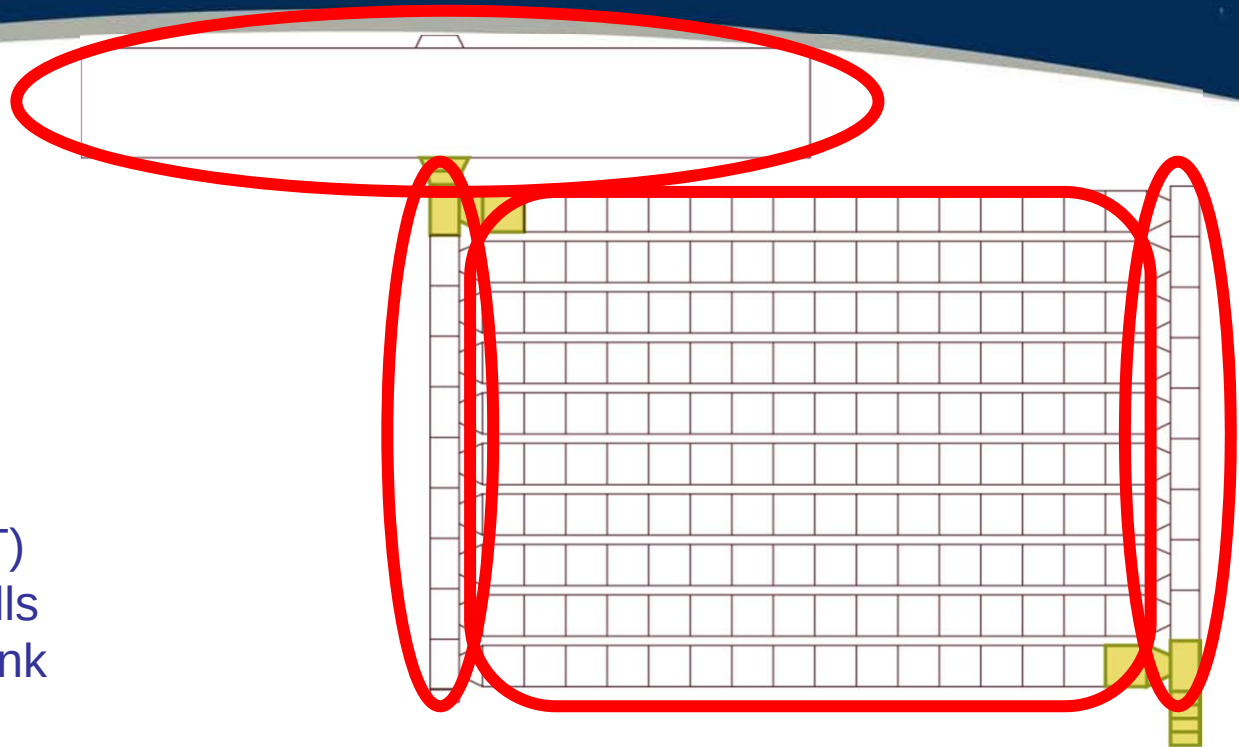
- u = Ultra-high speed
 - CMOS for ease of use and readout speed
 - CCD for in-pixel storage
 - Start from Tower 180 nm CIS process with dual gate oxide: 3nm + 10nm
 - Optimise process for high-speed, high-efficiency charge transfer
-



Photodiode

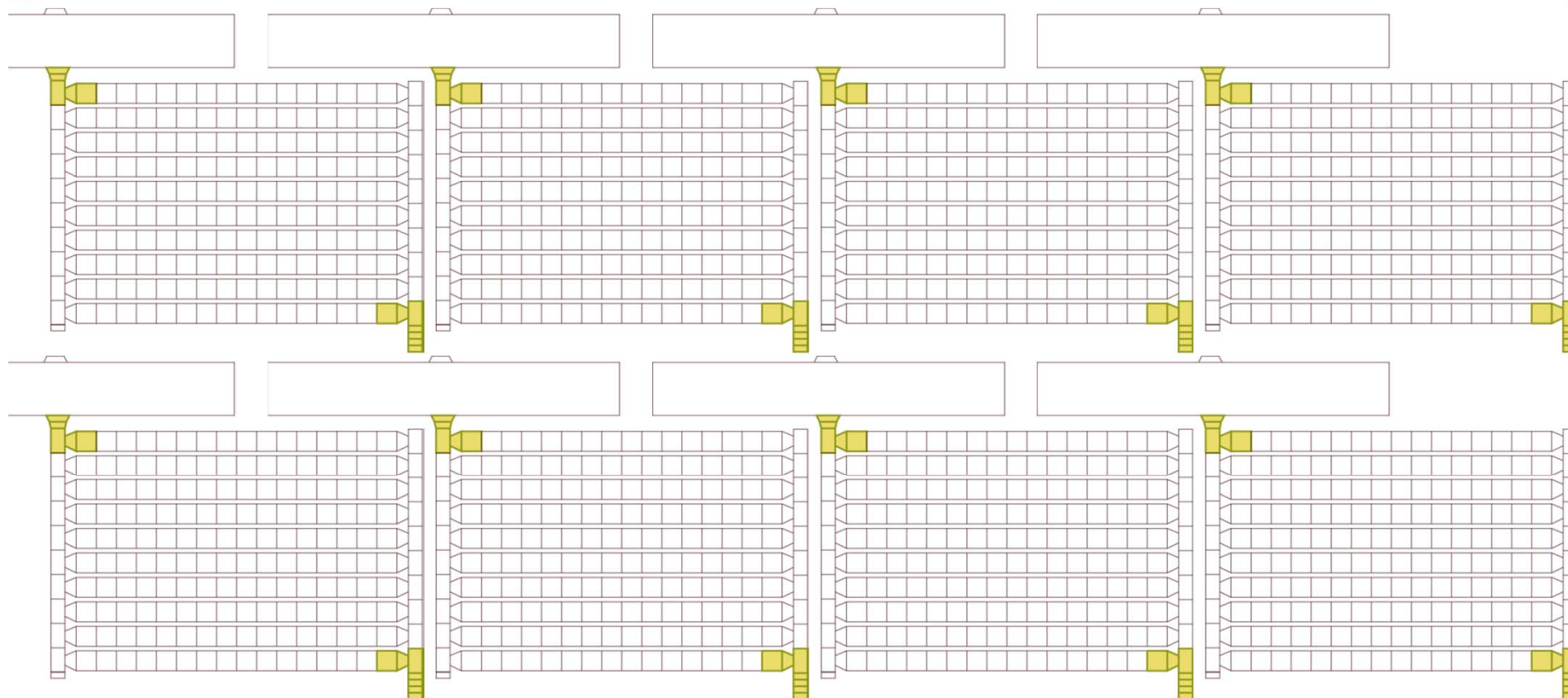
Memory bank

- A vertical entry (VEN) bank with 10 cells
- Ten rows of lateral (LAT) banks, each with 16 cells
- A vertical exit (VEX) bank with 10 cells
- Total of 180 memory cells





Kirana pixel. 2

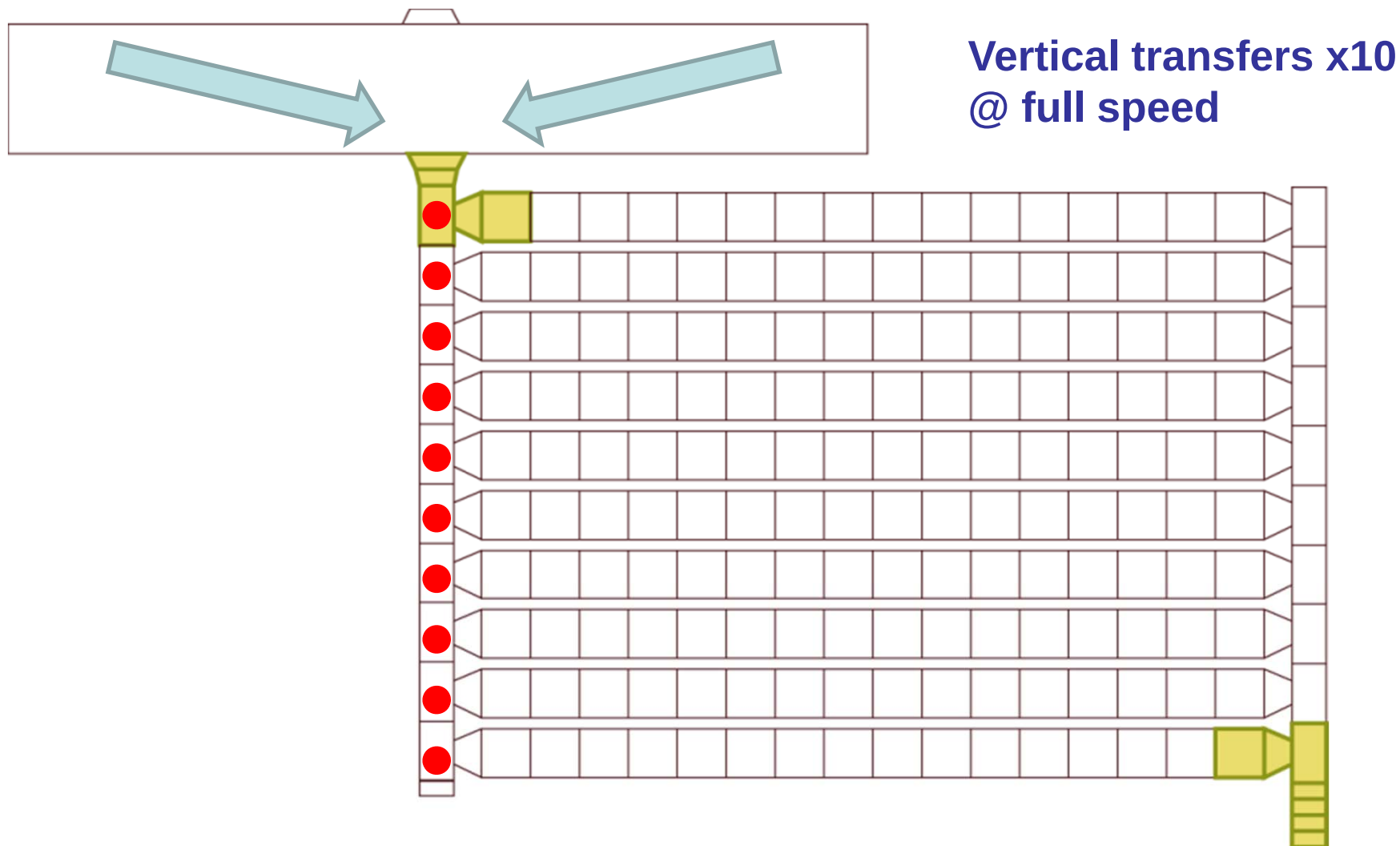


Highly scalable architecture:

- Number of memory cells
- Number of pixels

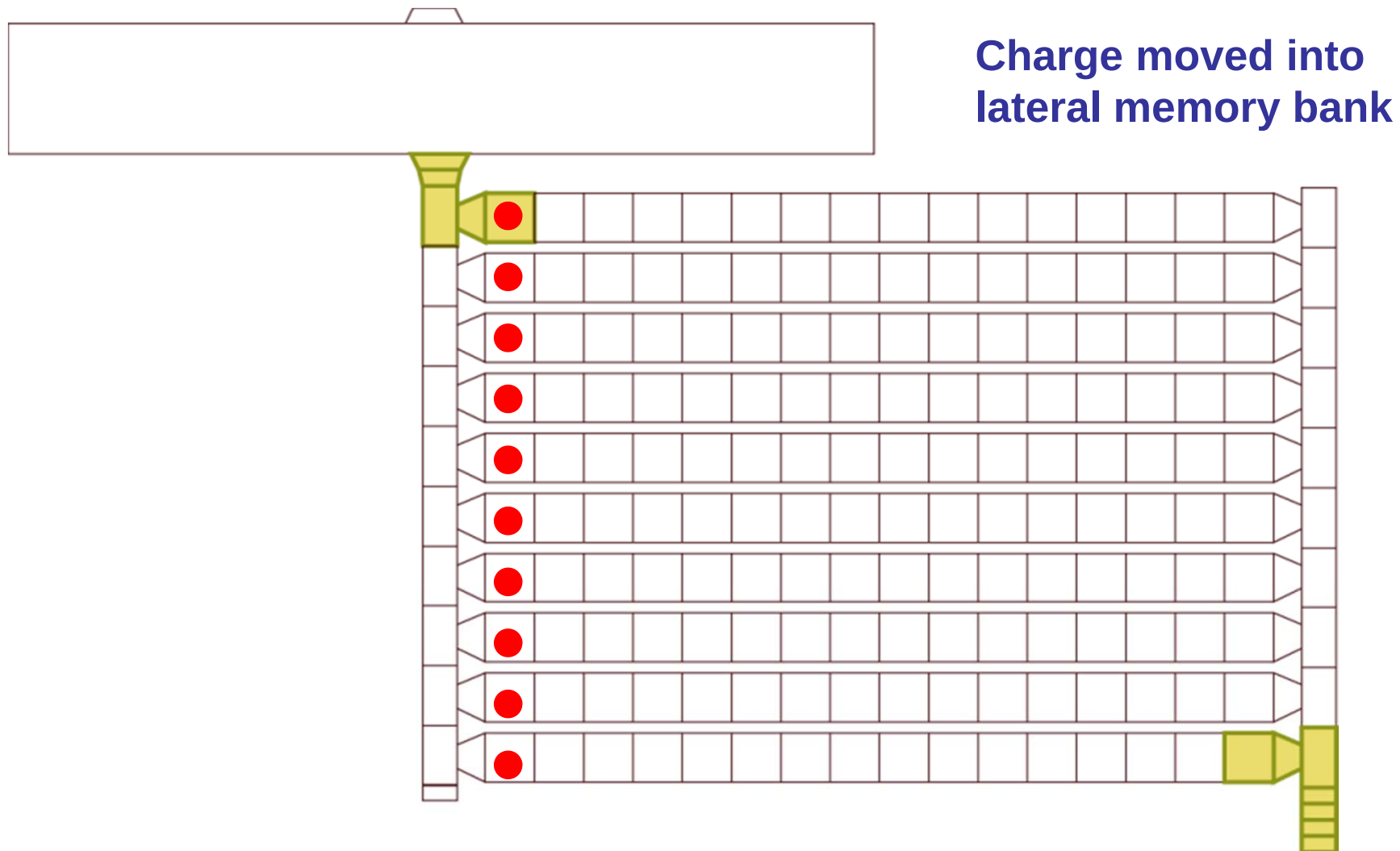


Burst mode



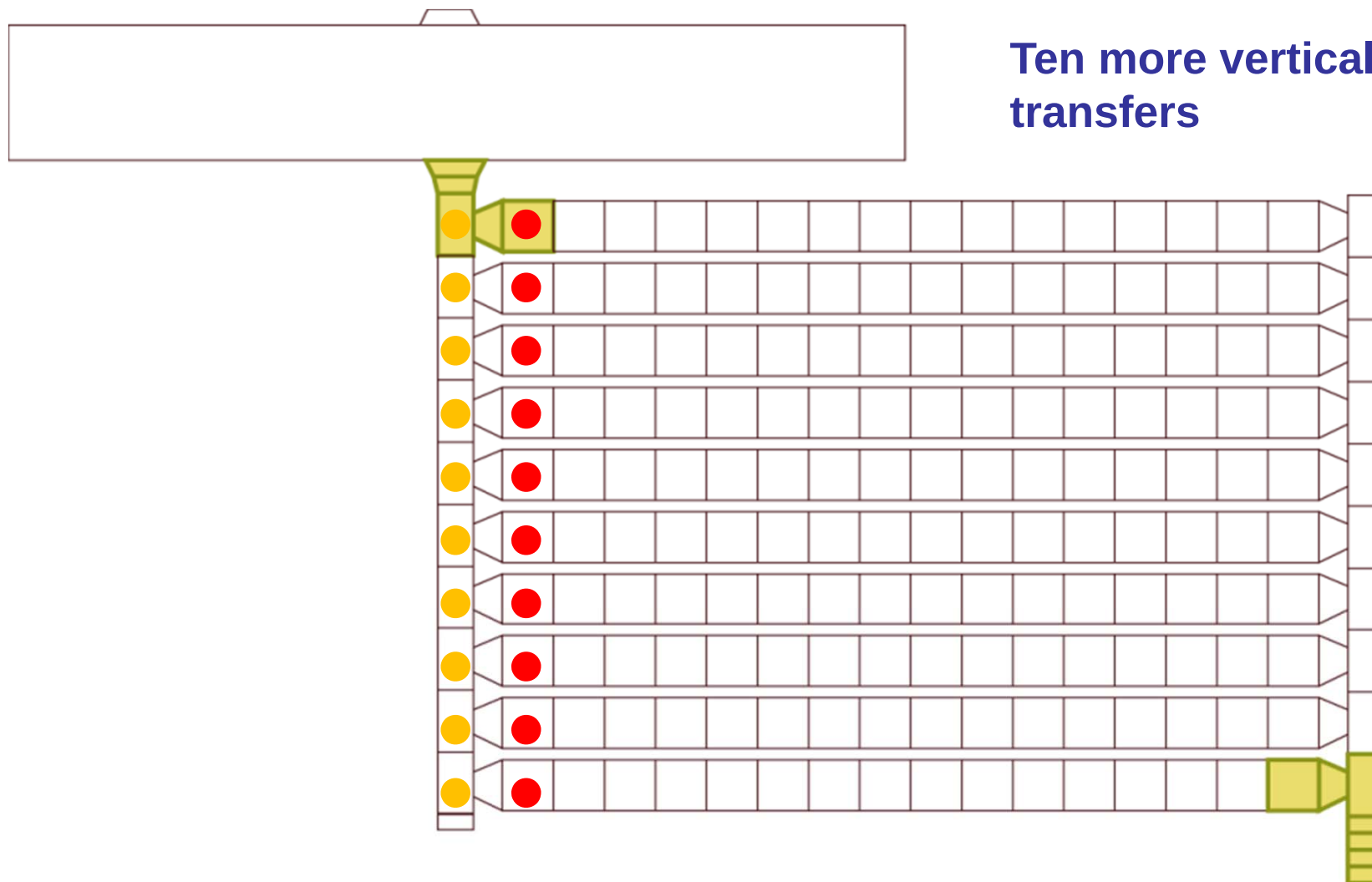


Burst mode



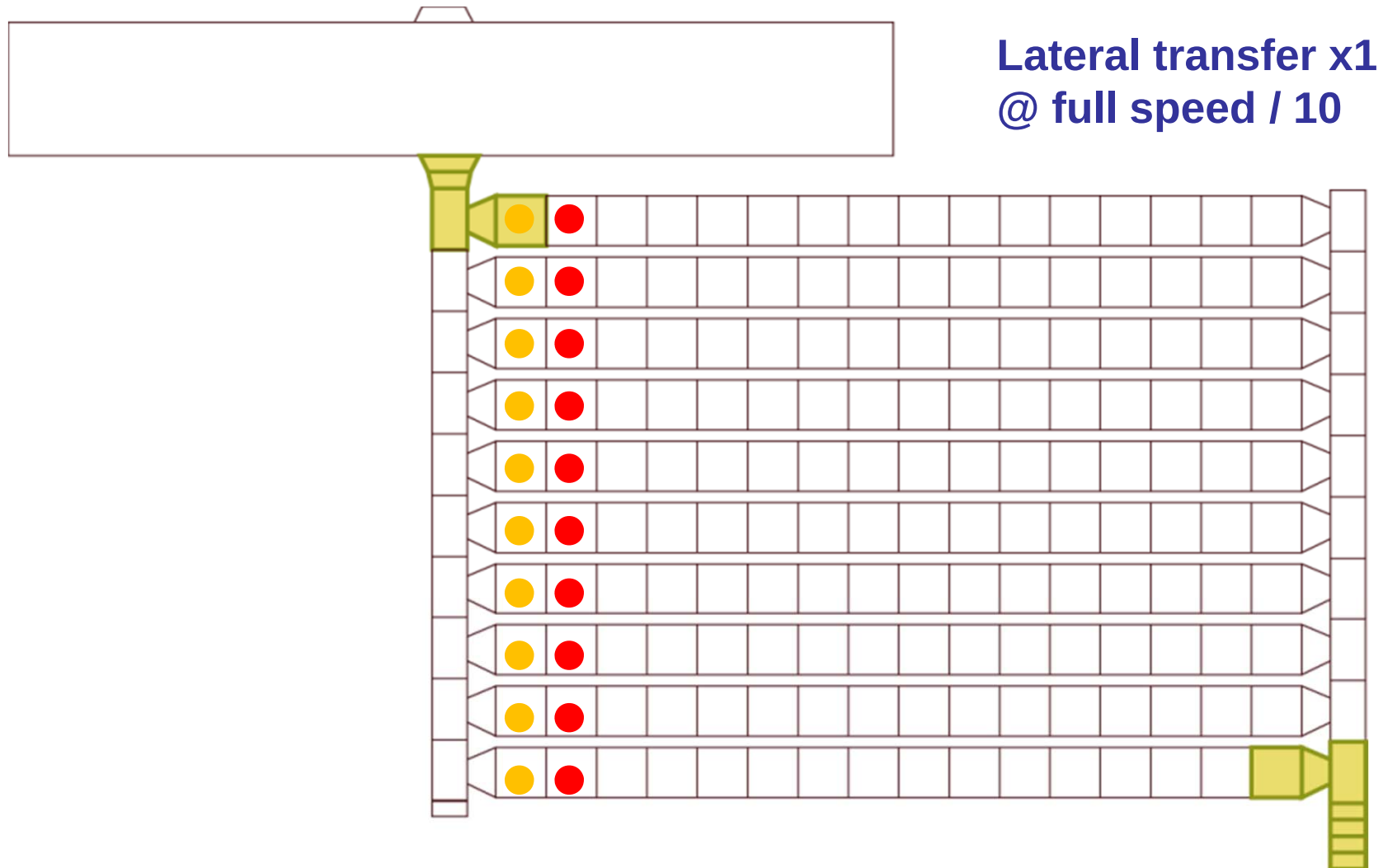


Burst mode



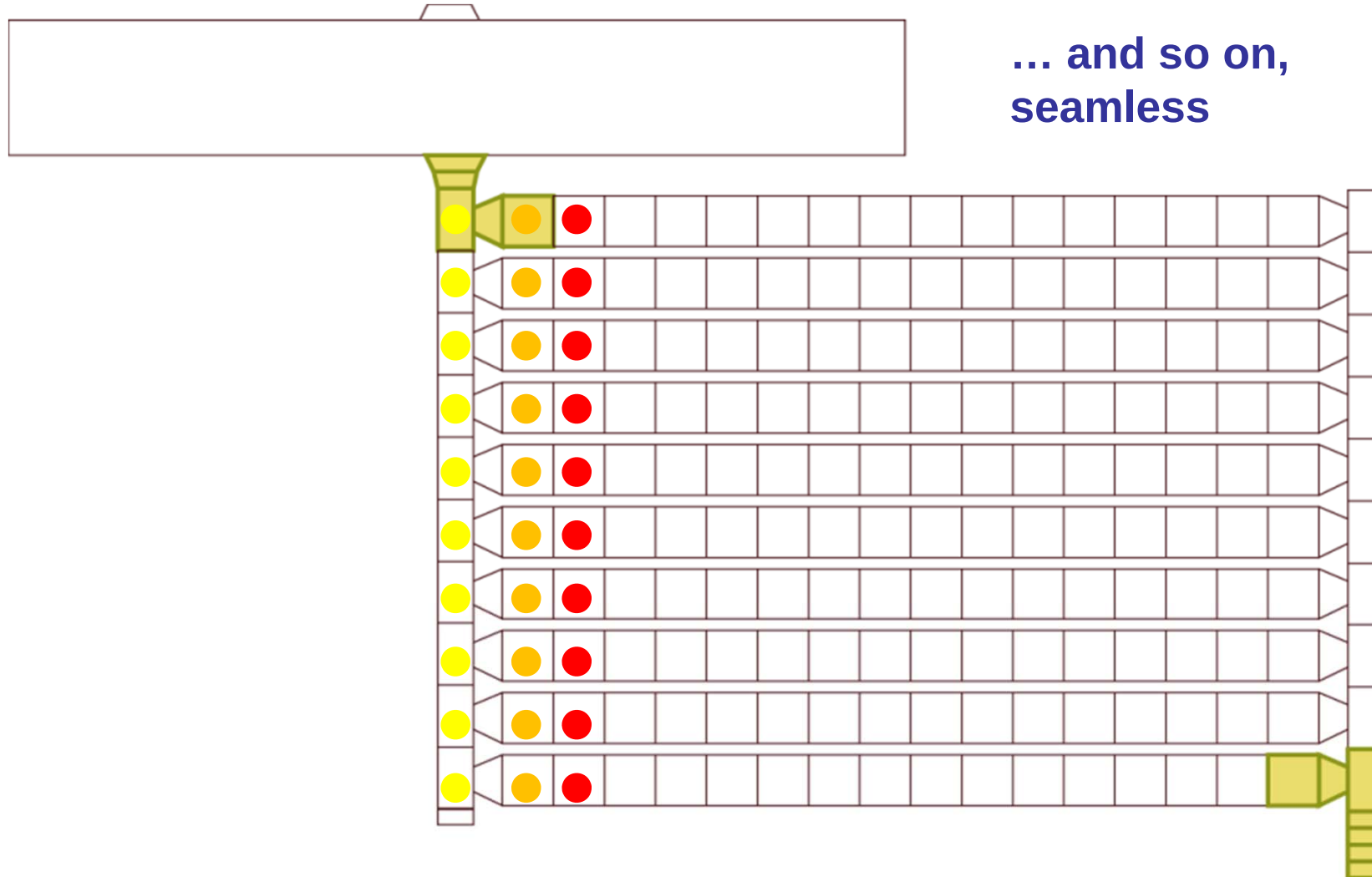


Burst mode



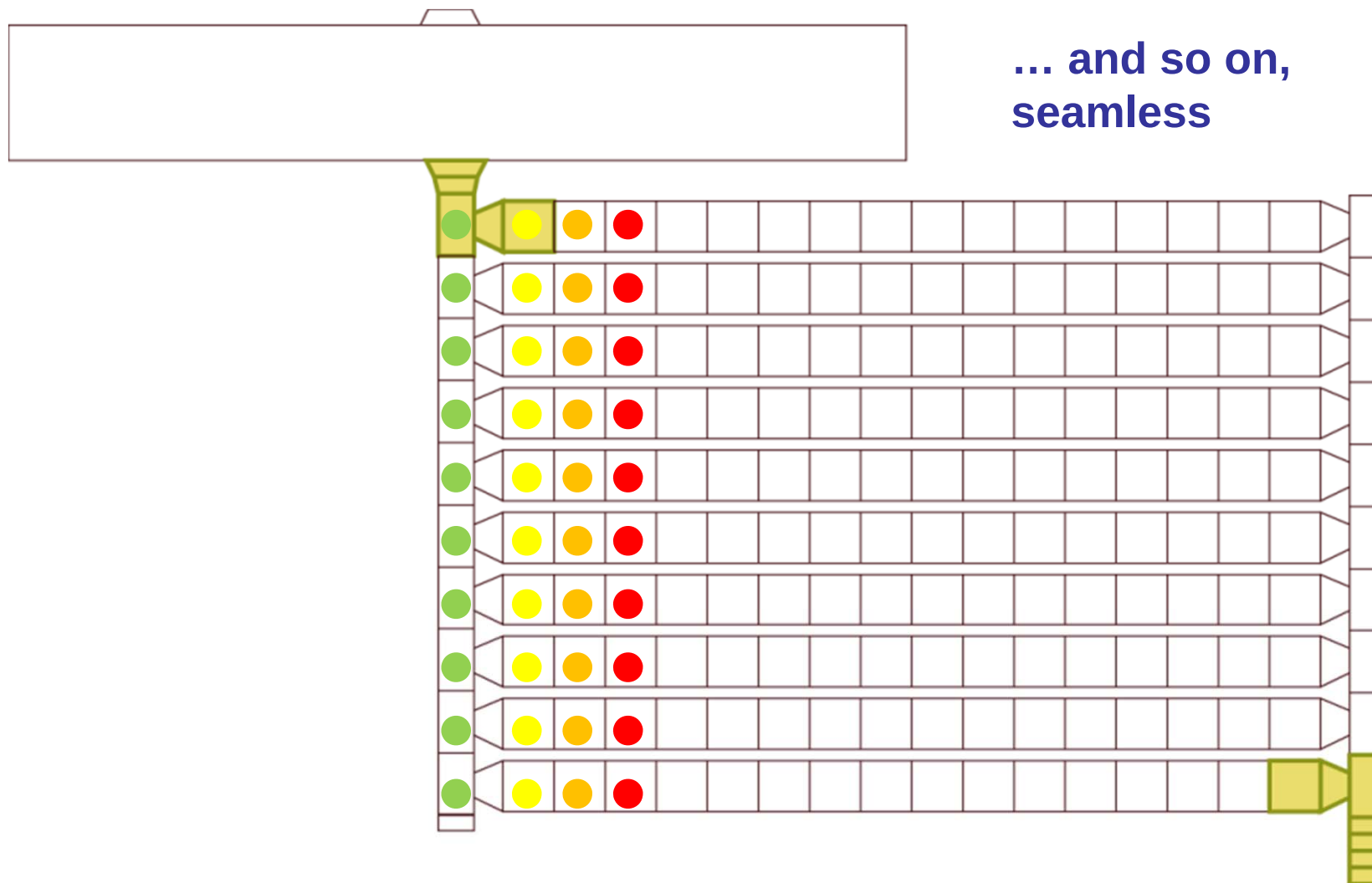


Burst mode



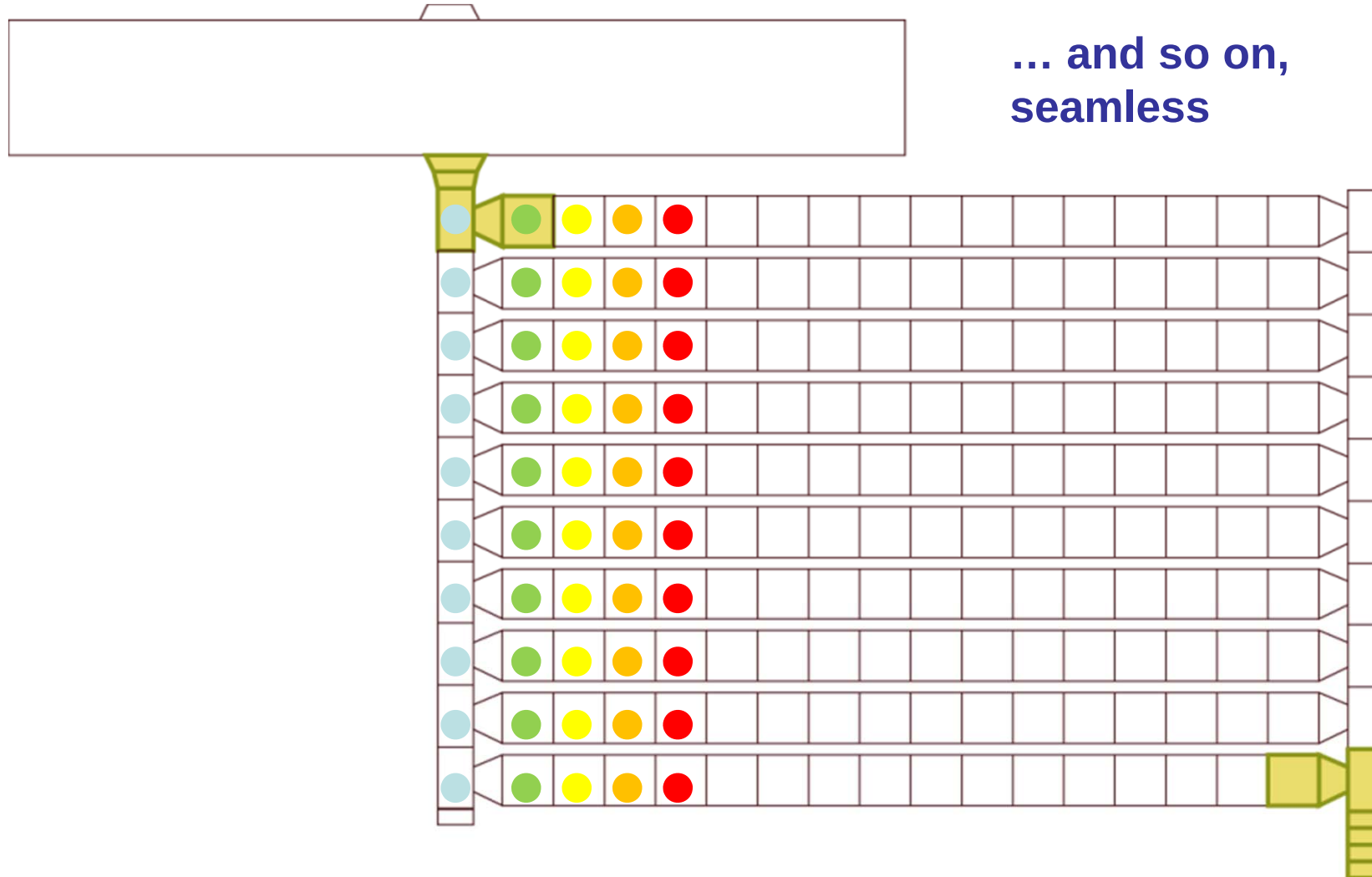


Burst mode



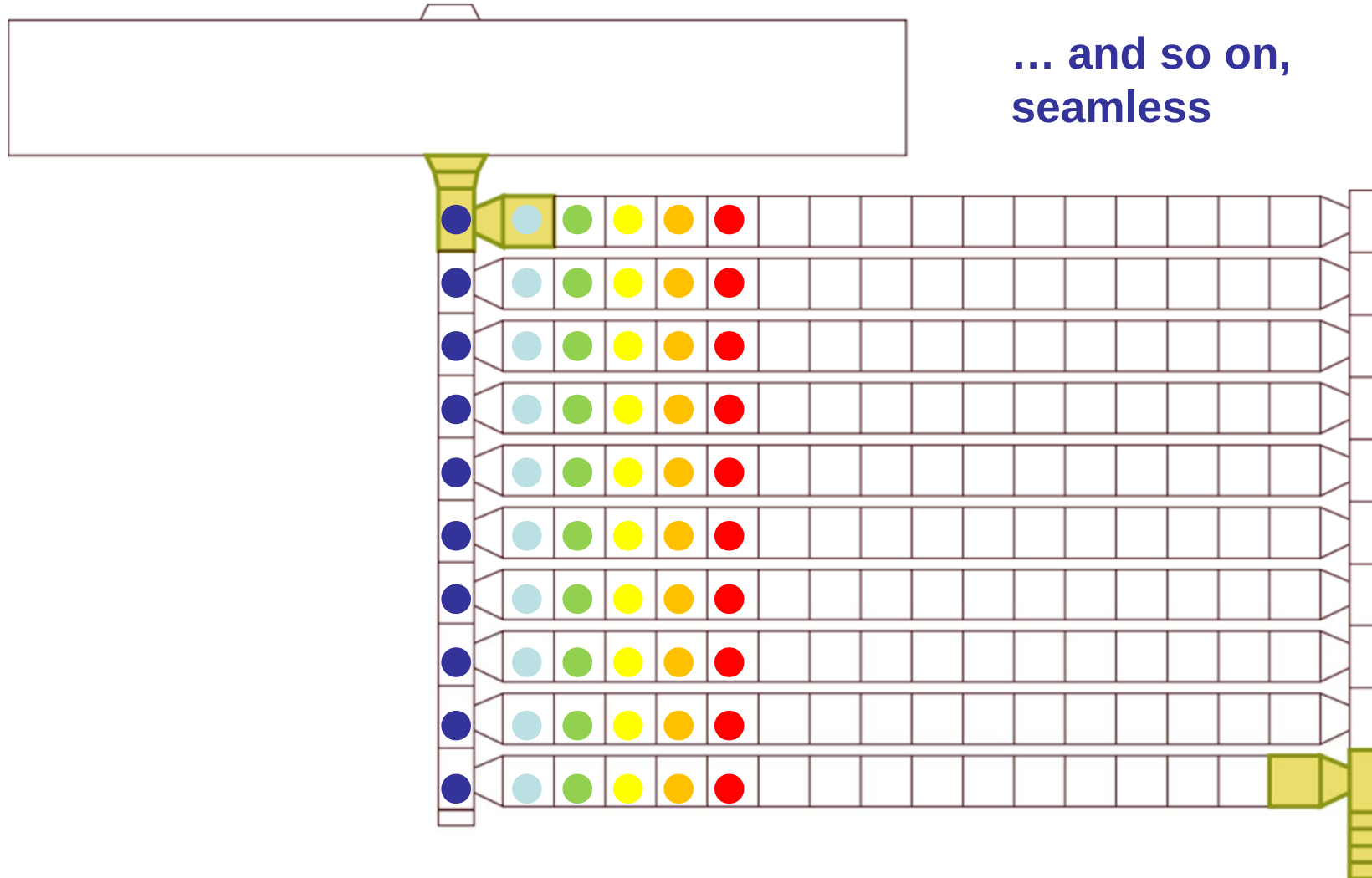


Burst mode



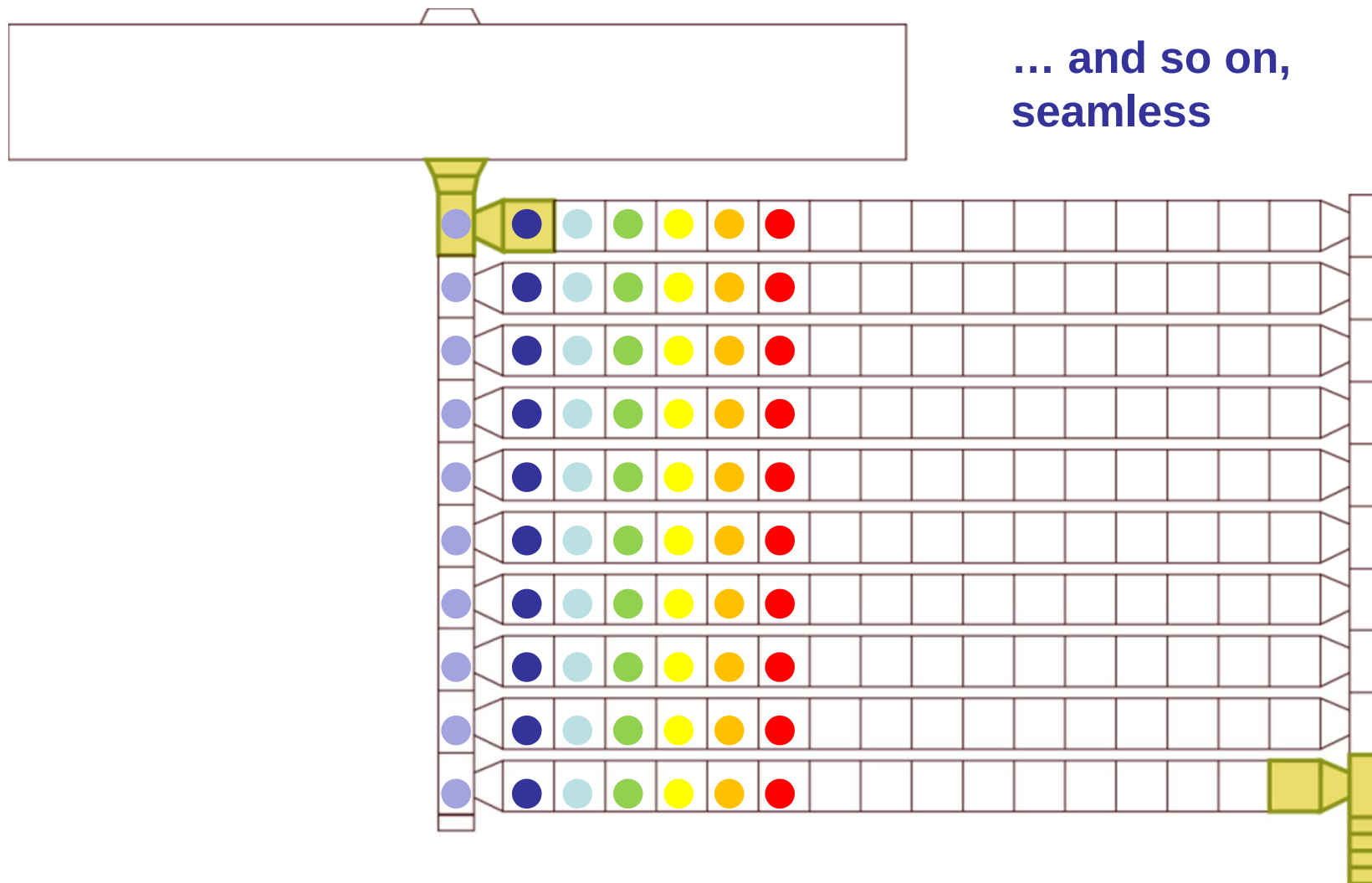


Burst mode

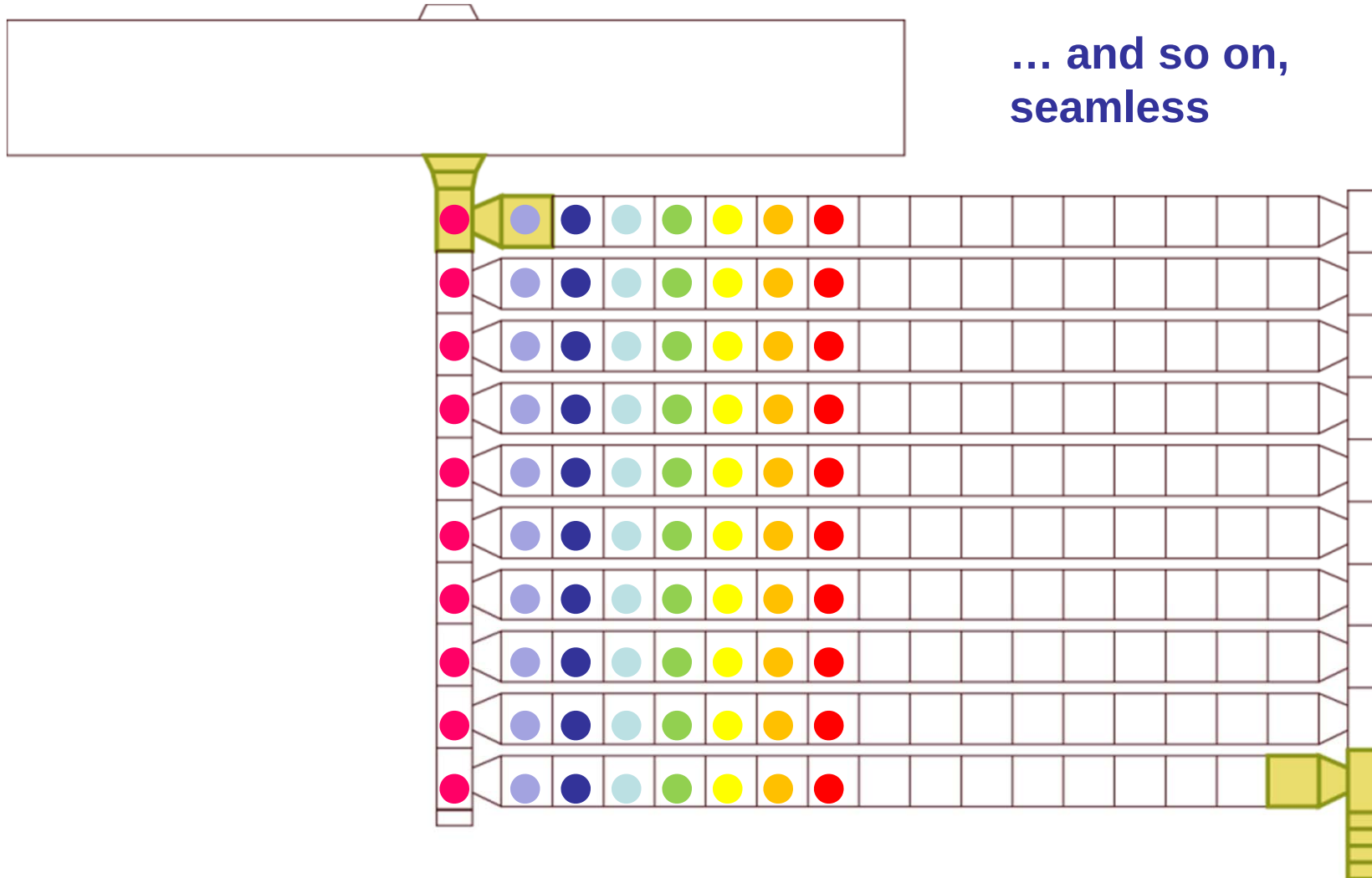




Burst mode

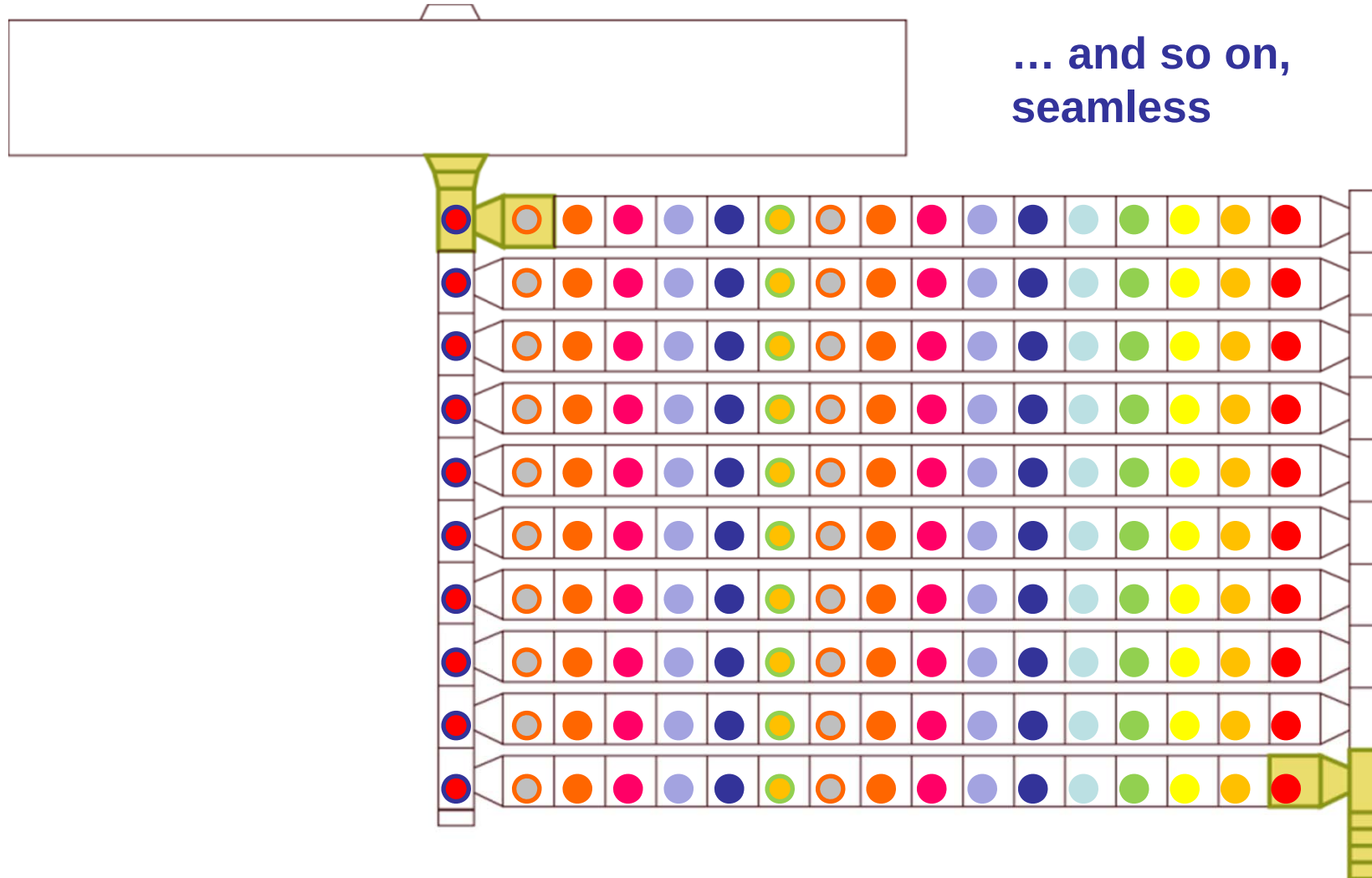


**... and so on,
seamless**



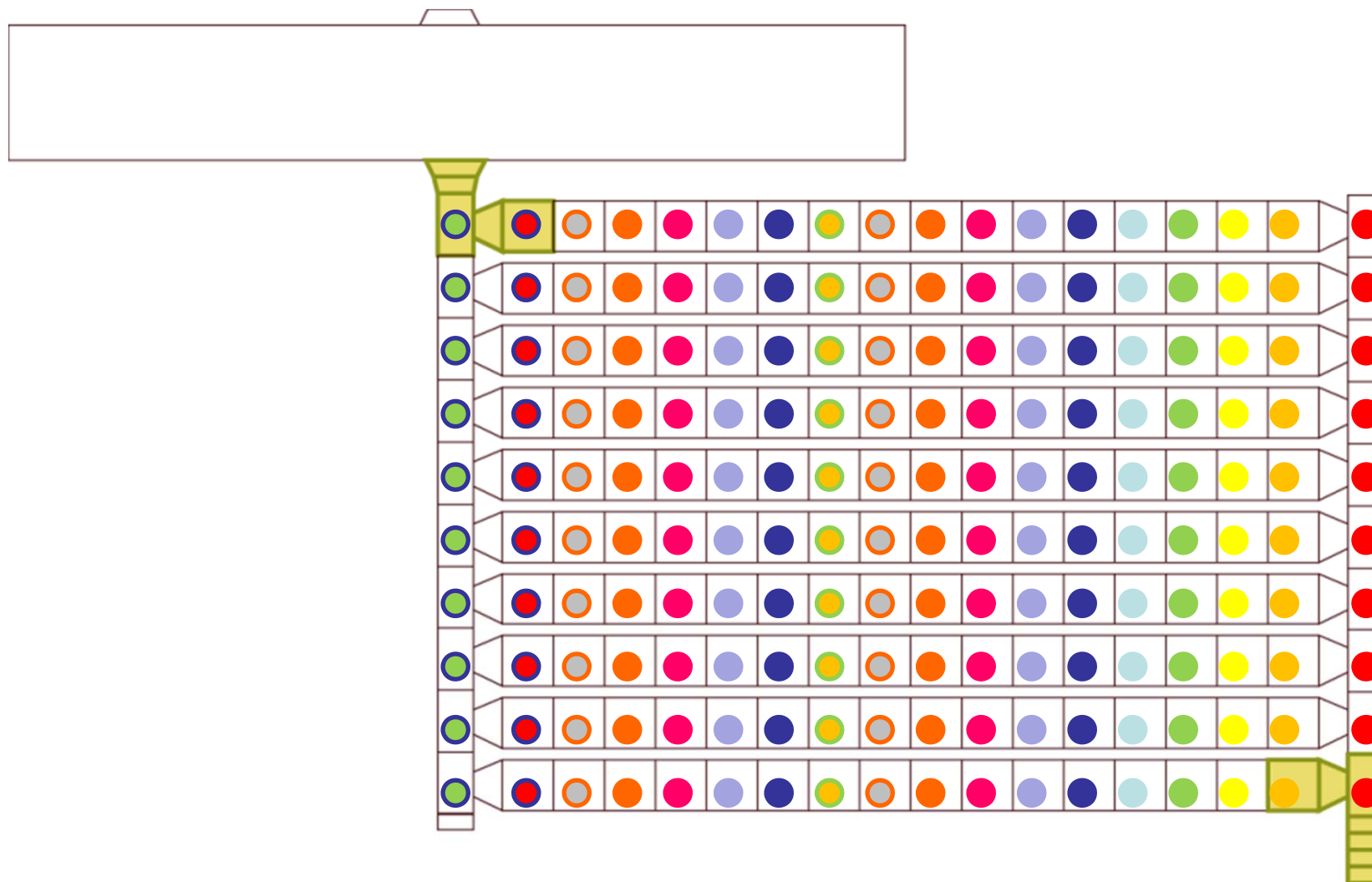


Burst mode



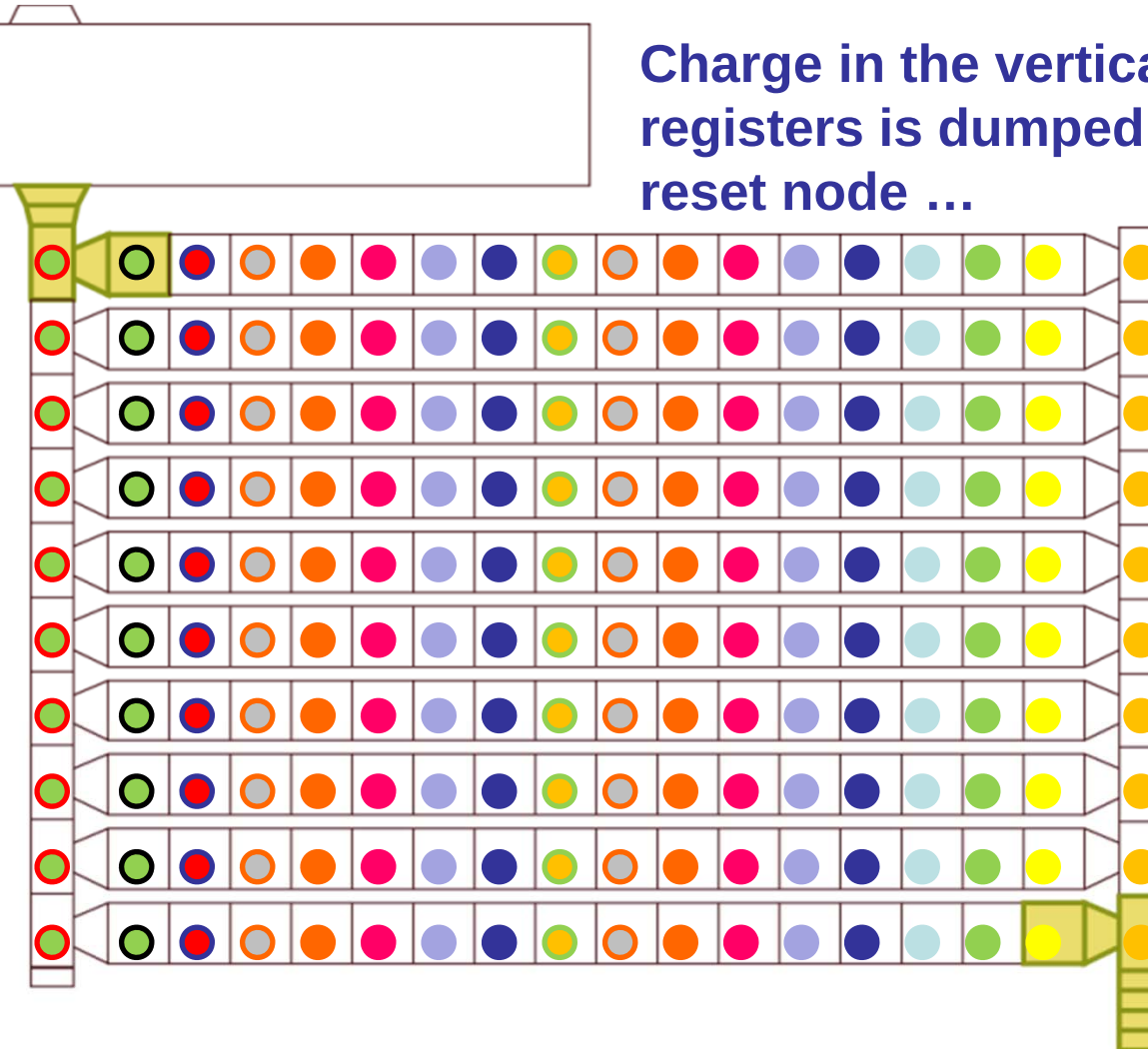


Burst mode



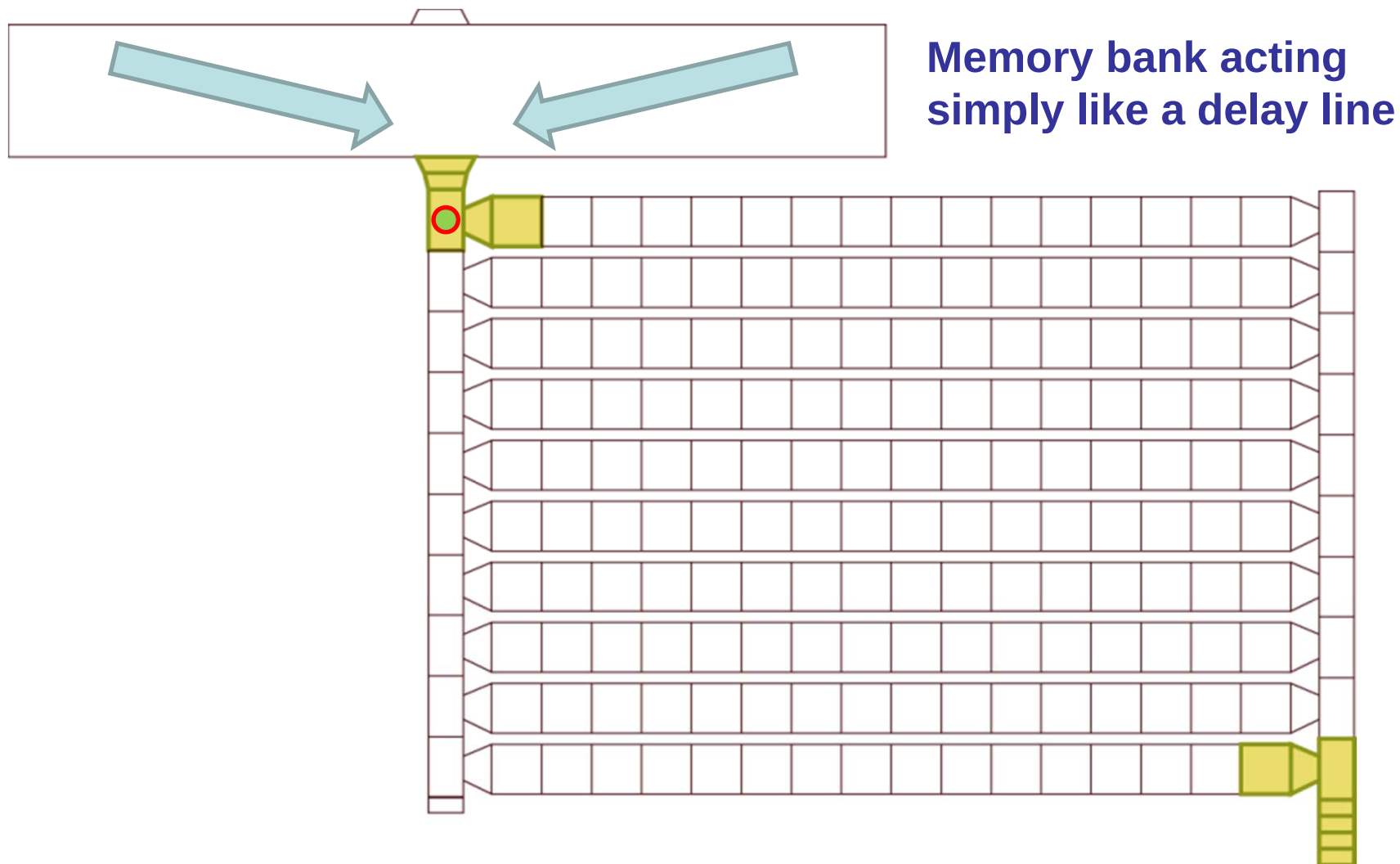
... until receipt of the trigger. The status of the memory bank is then frozen and the sensor read out.

Charge in the vertical exit registers is dumped in the reset node ...



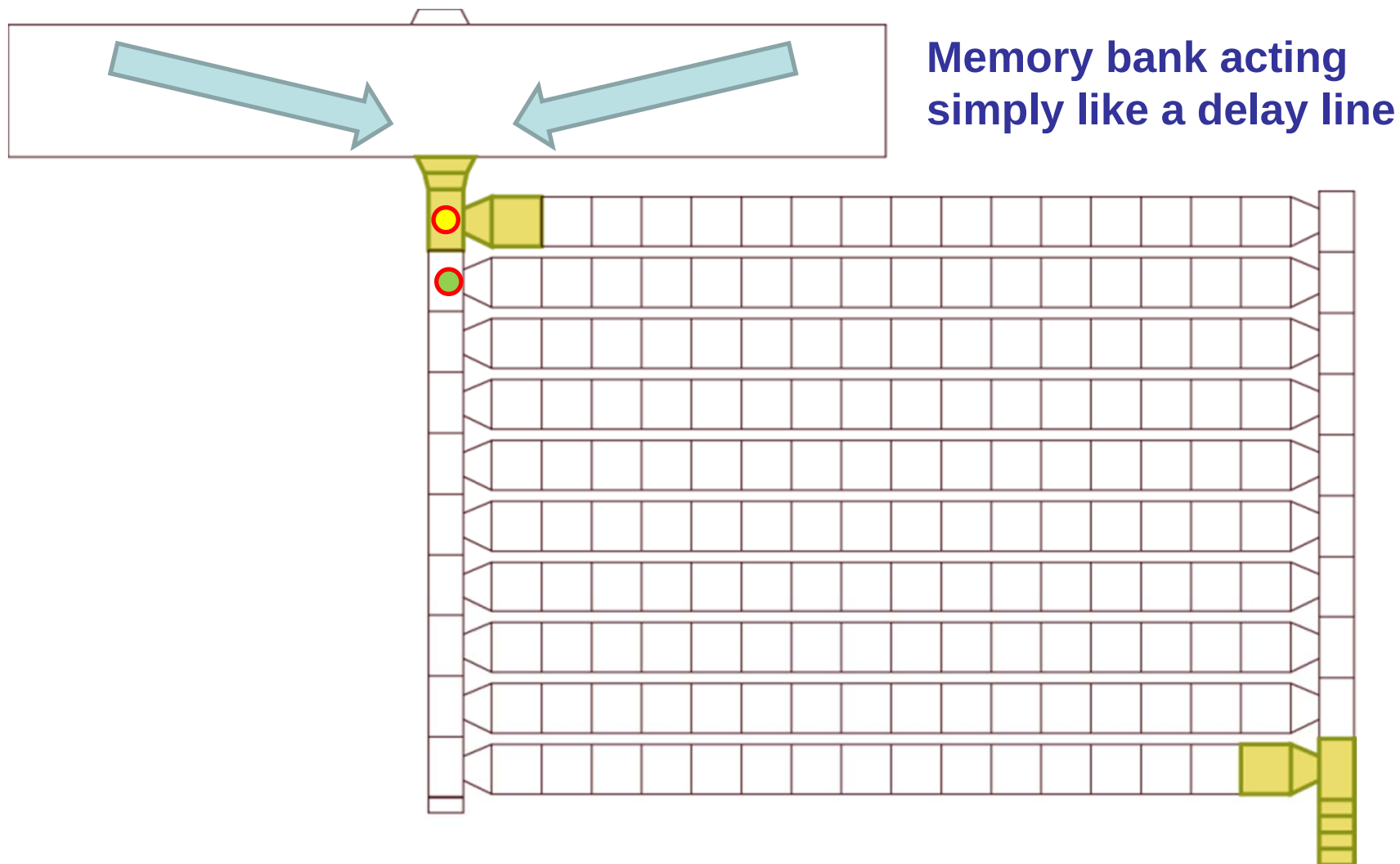


Continuous mode



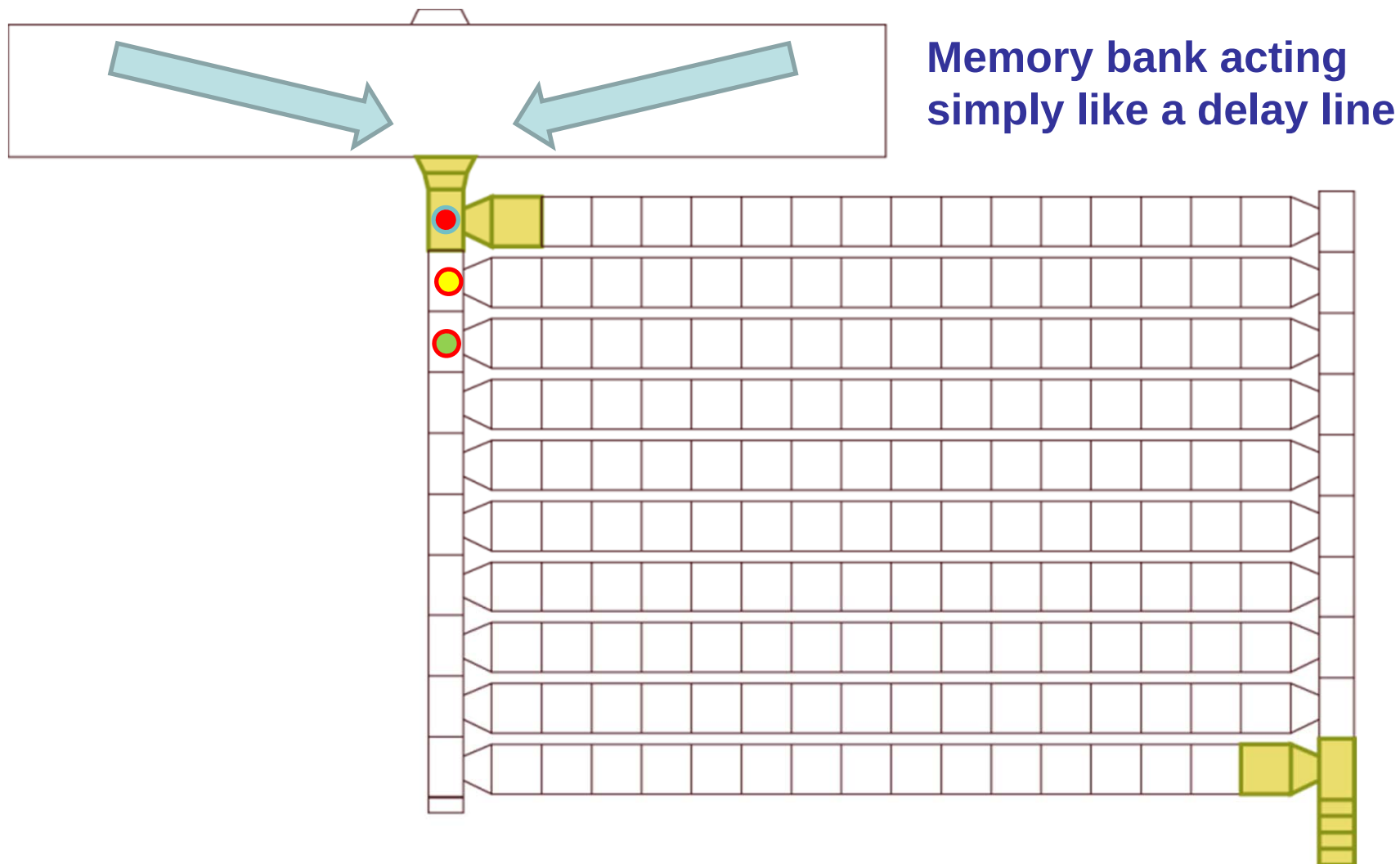


Continuous mode



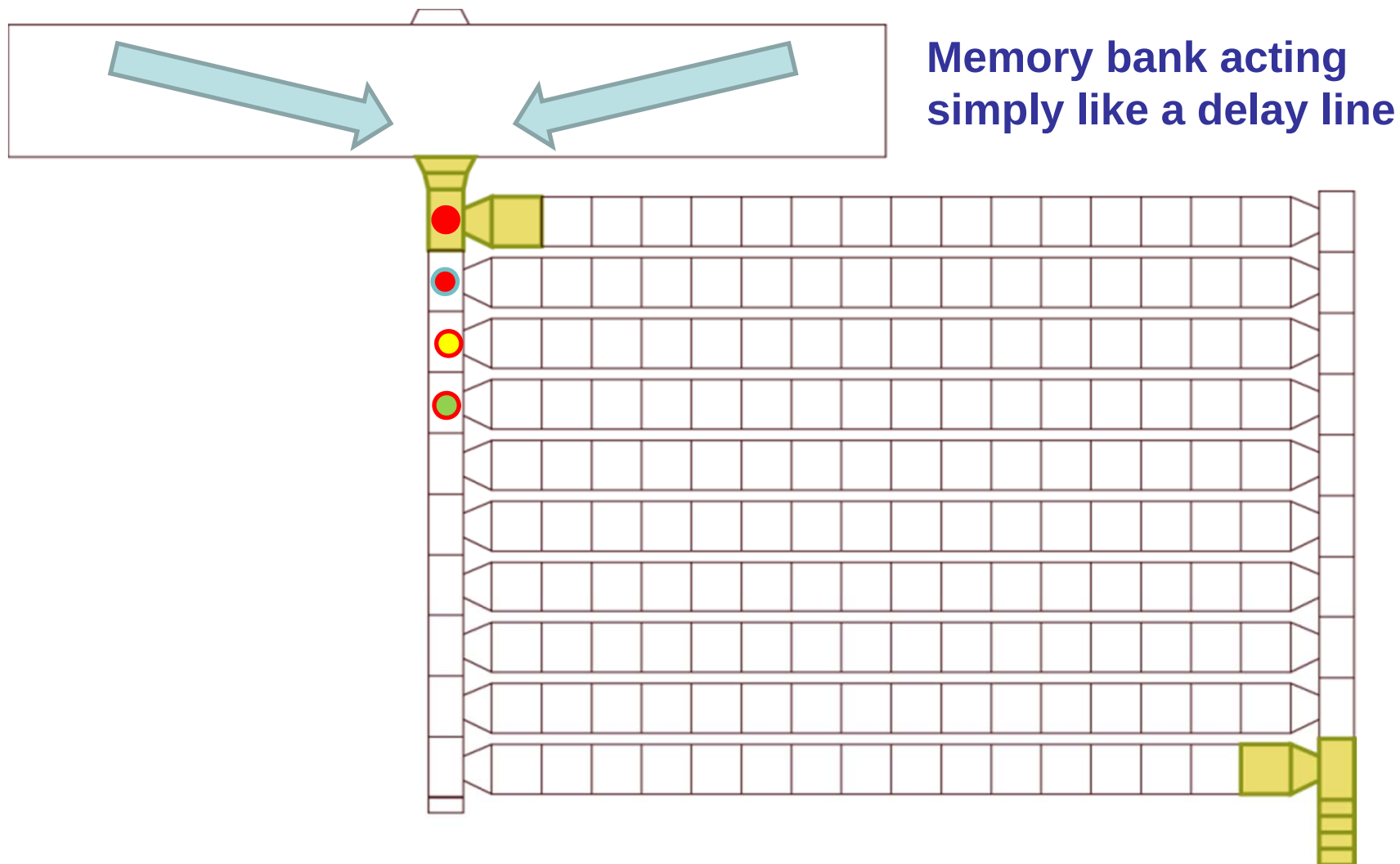


Continuous mode



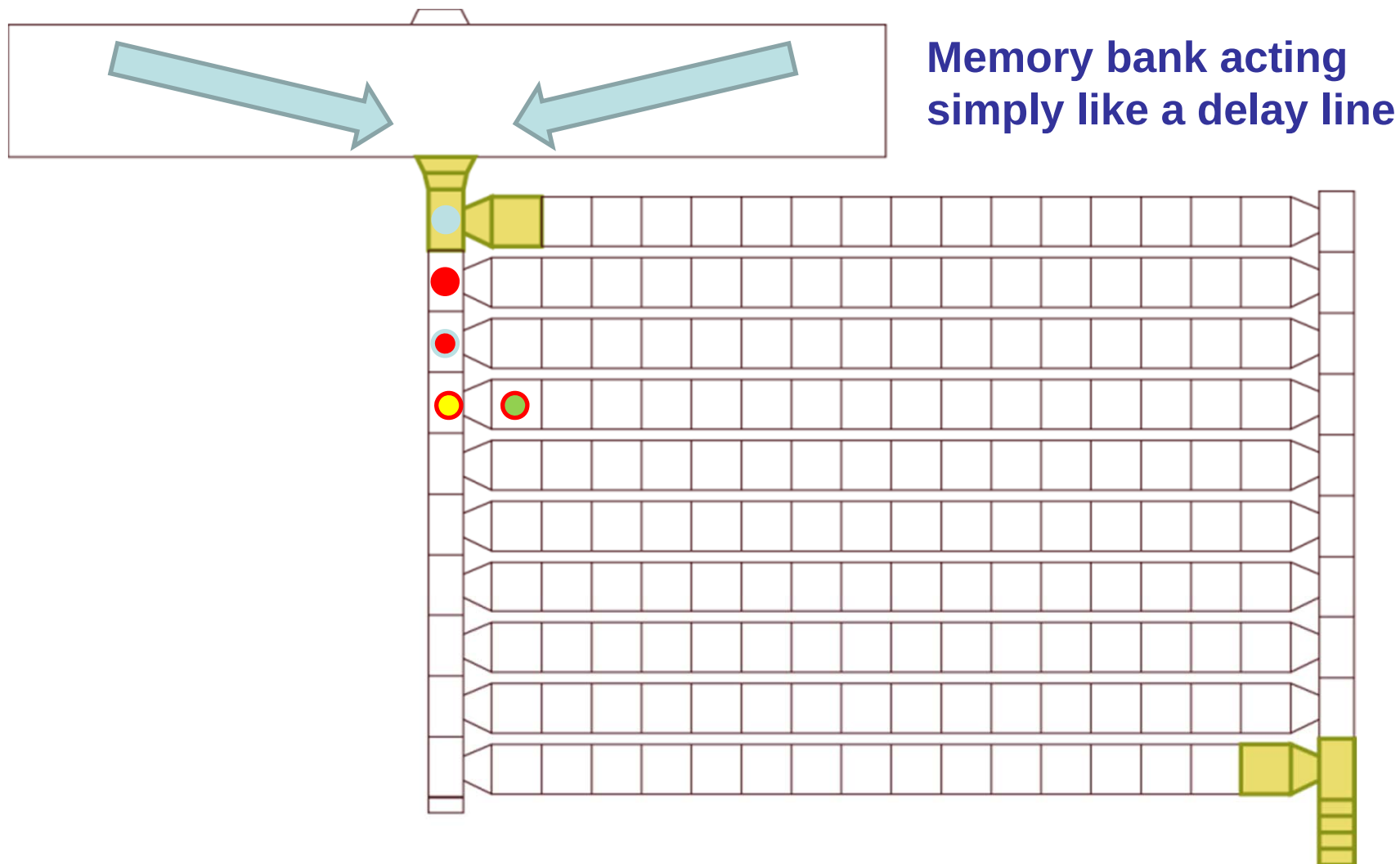


Continuous mode



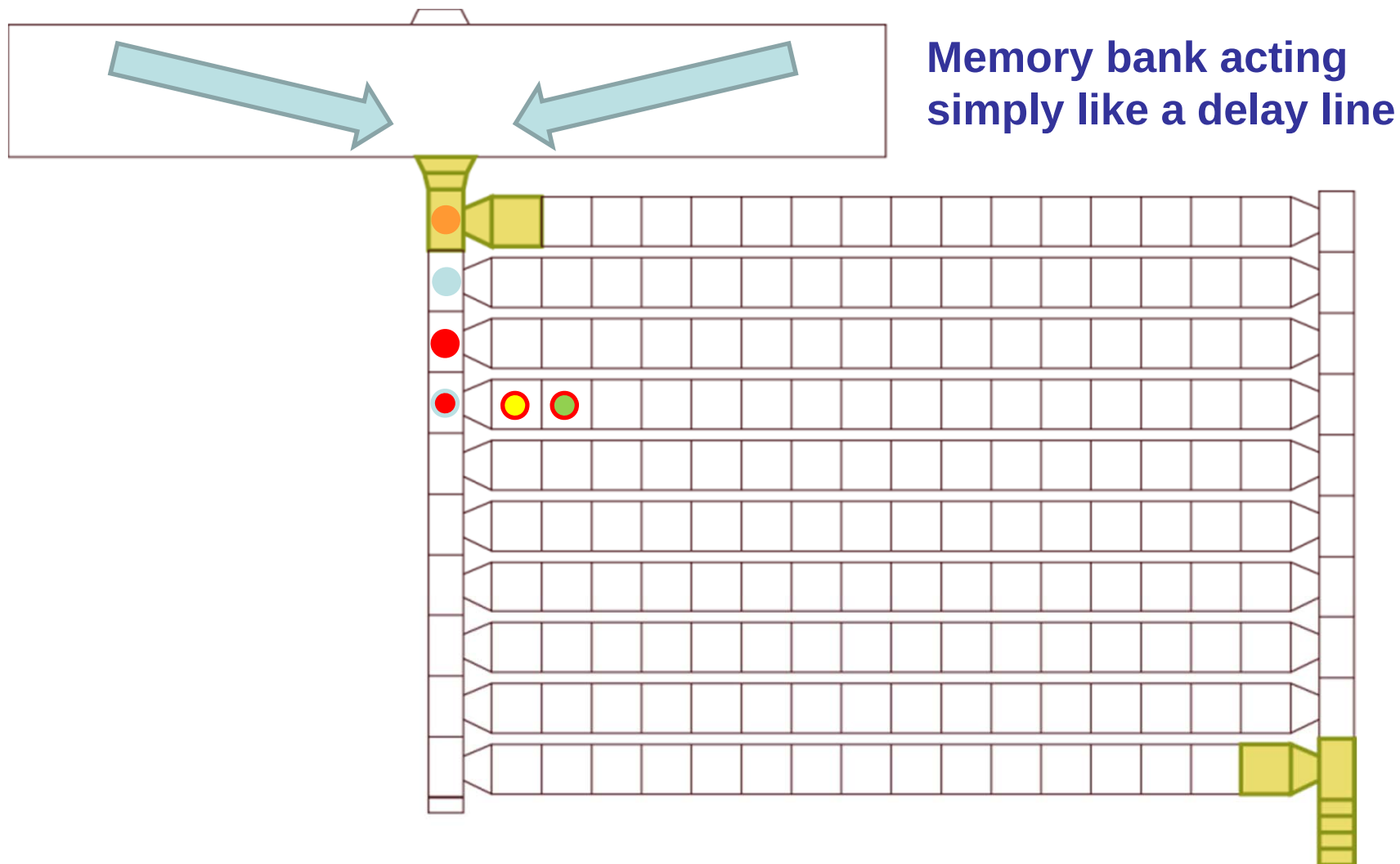


Continuous mode



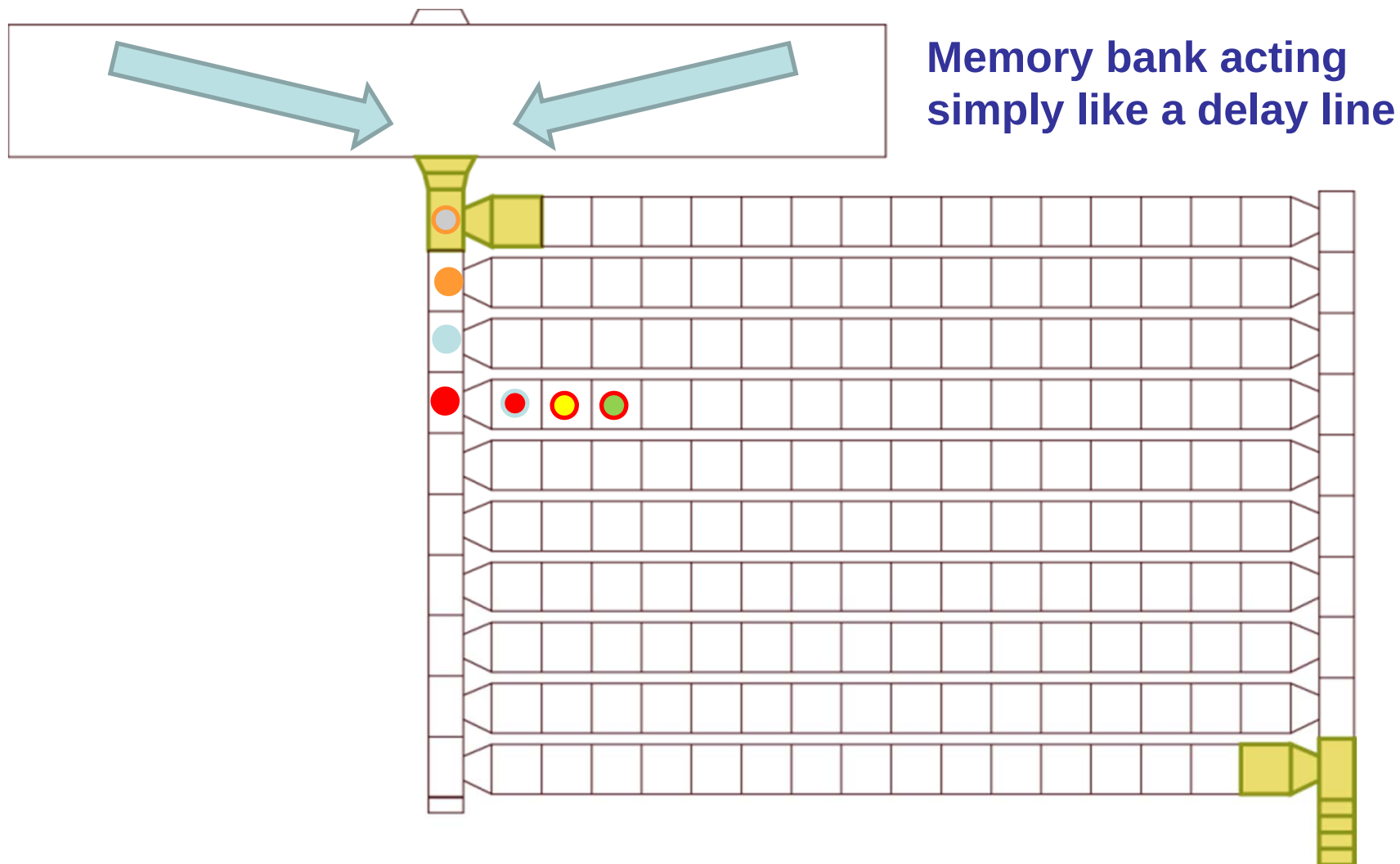


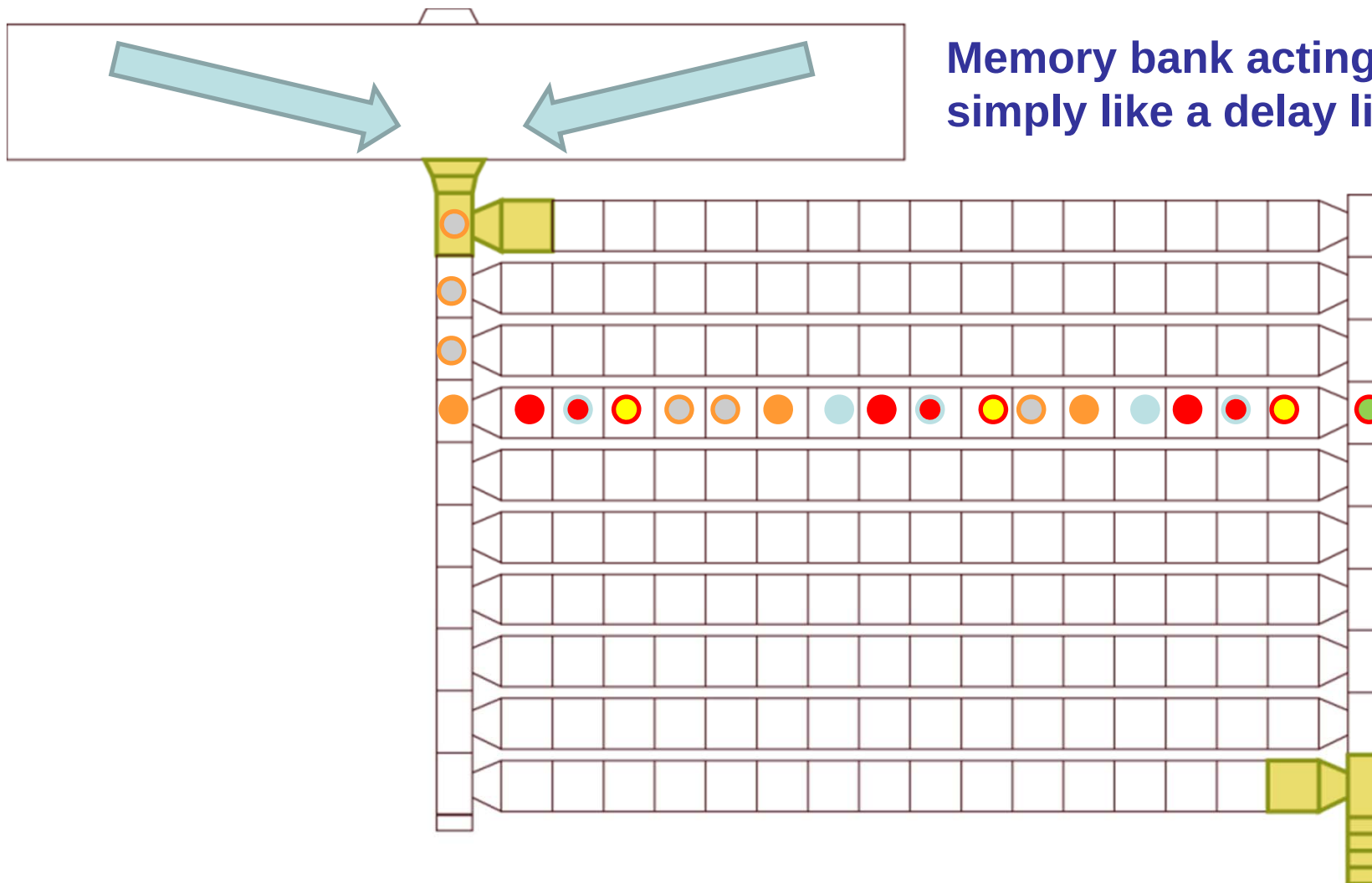
Continuous mode

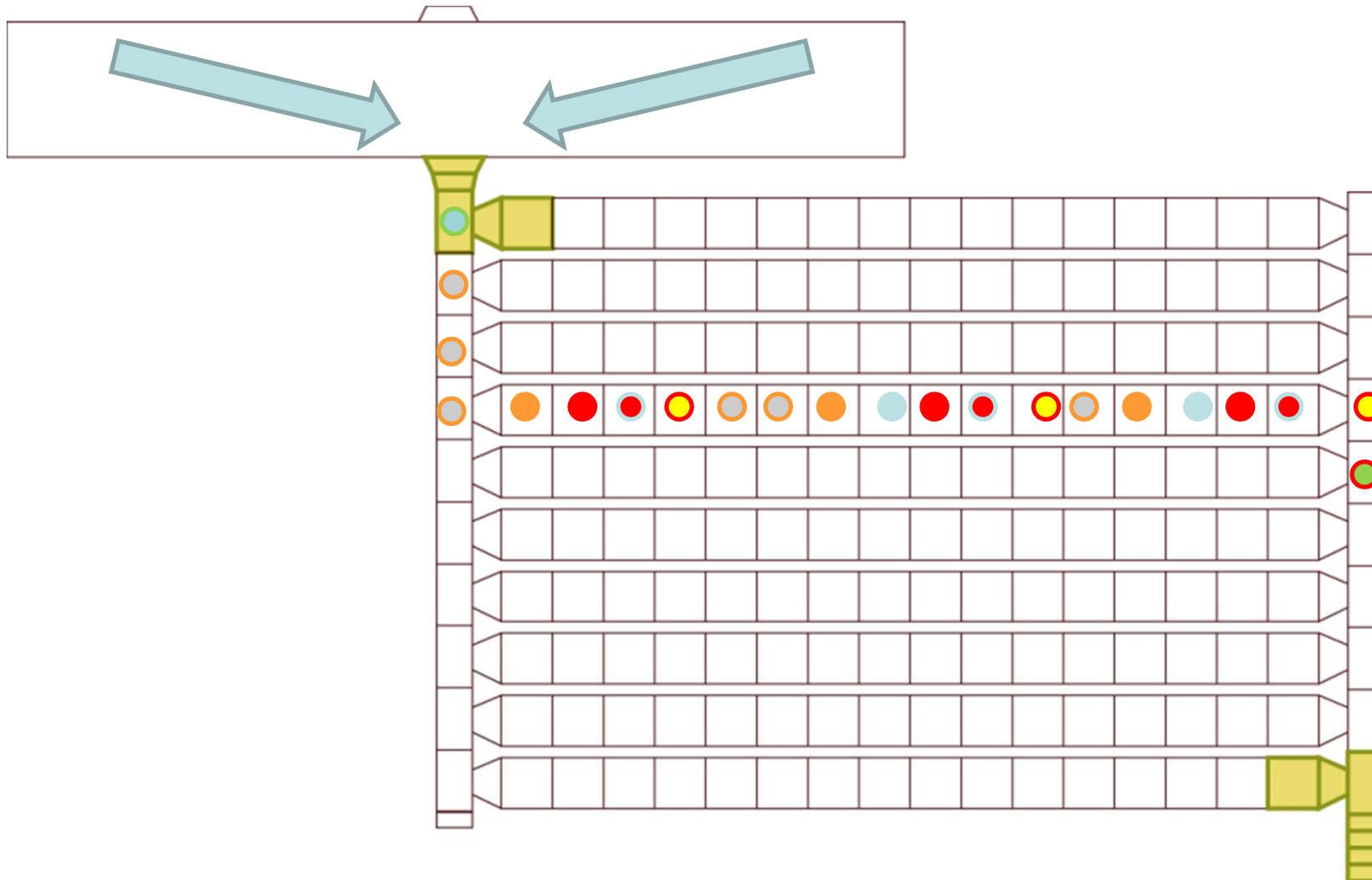




Continuous mode

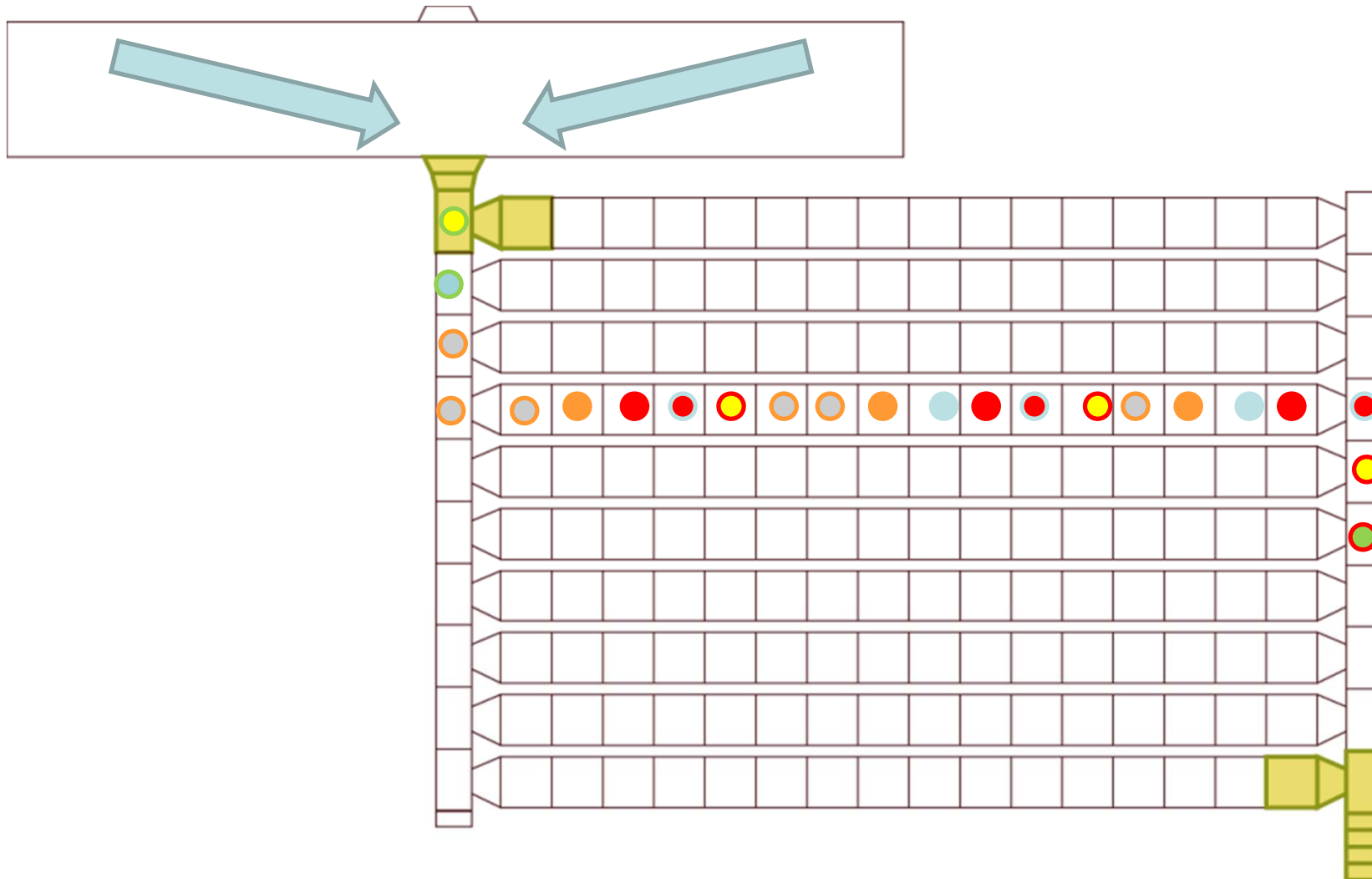






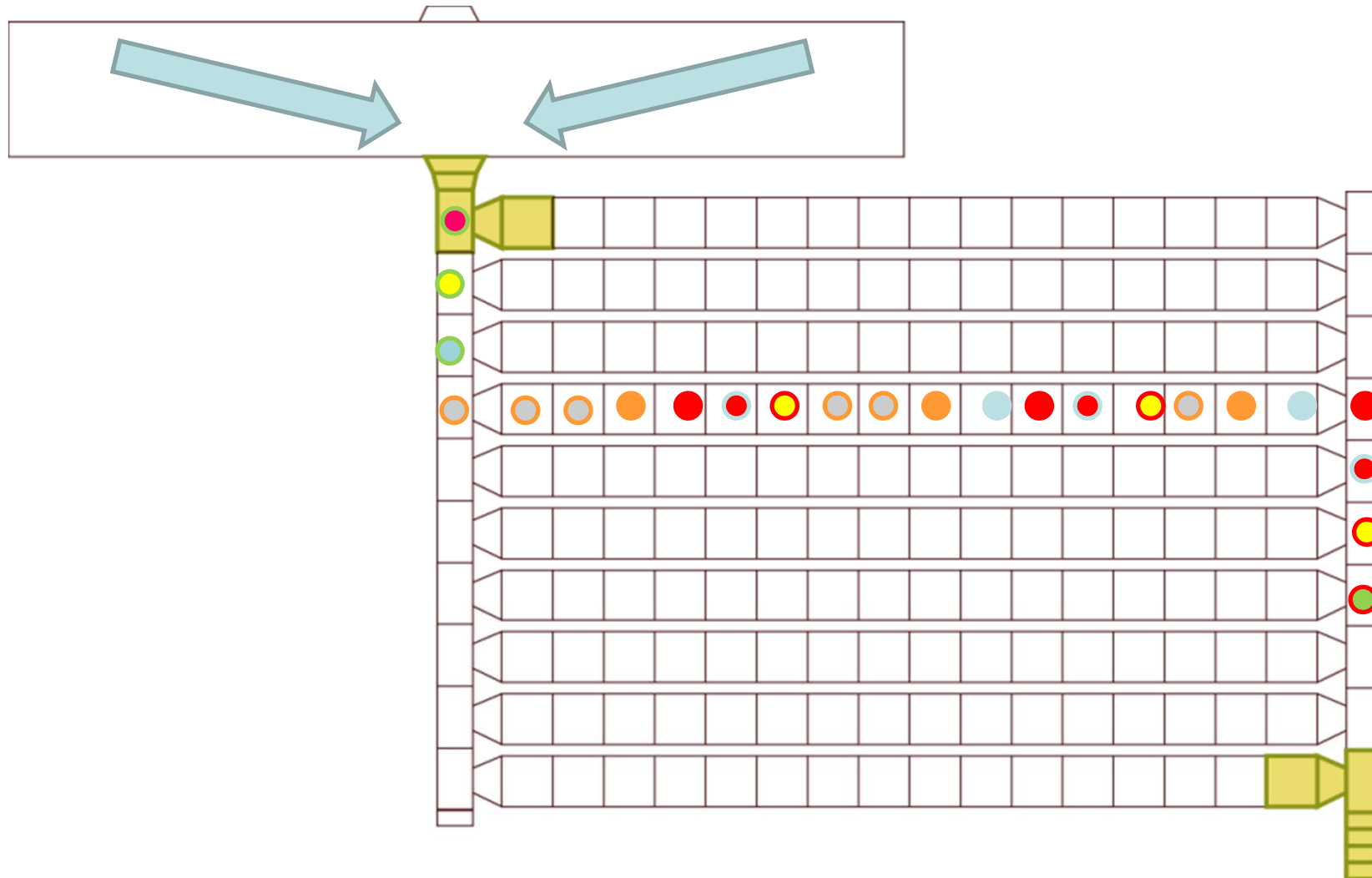


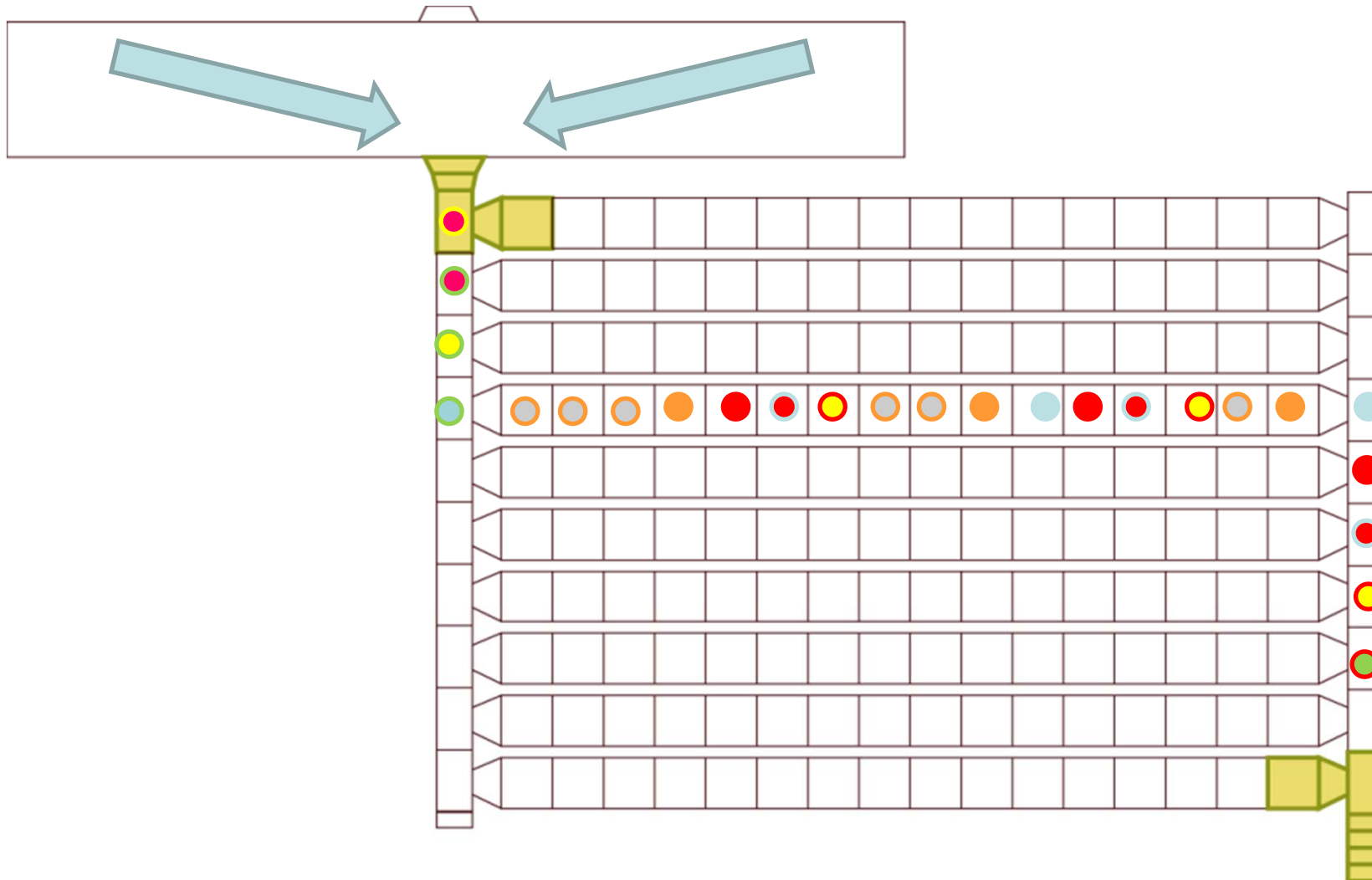
Continuous mode





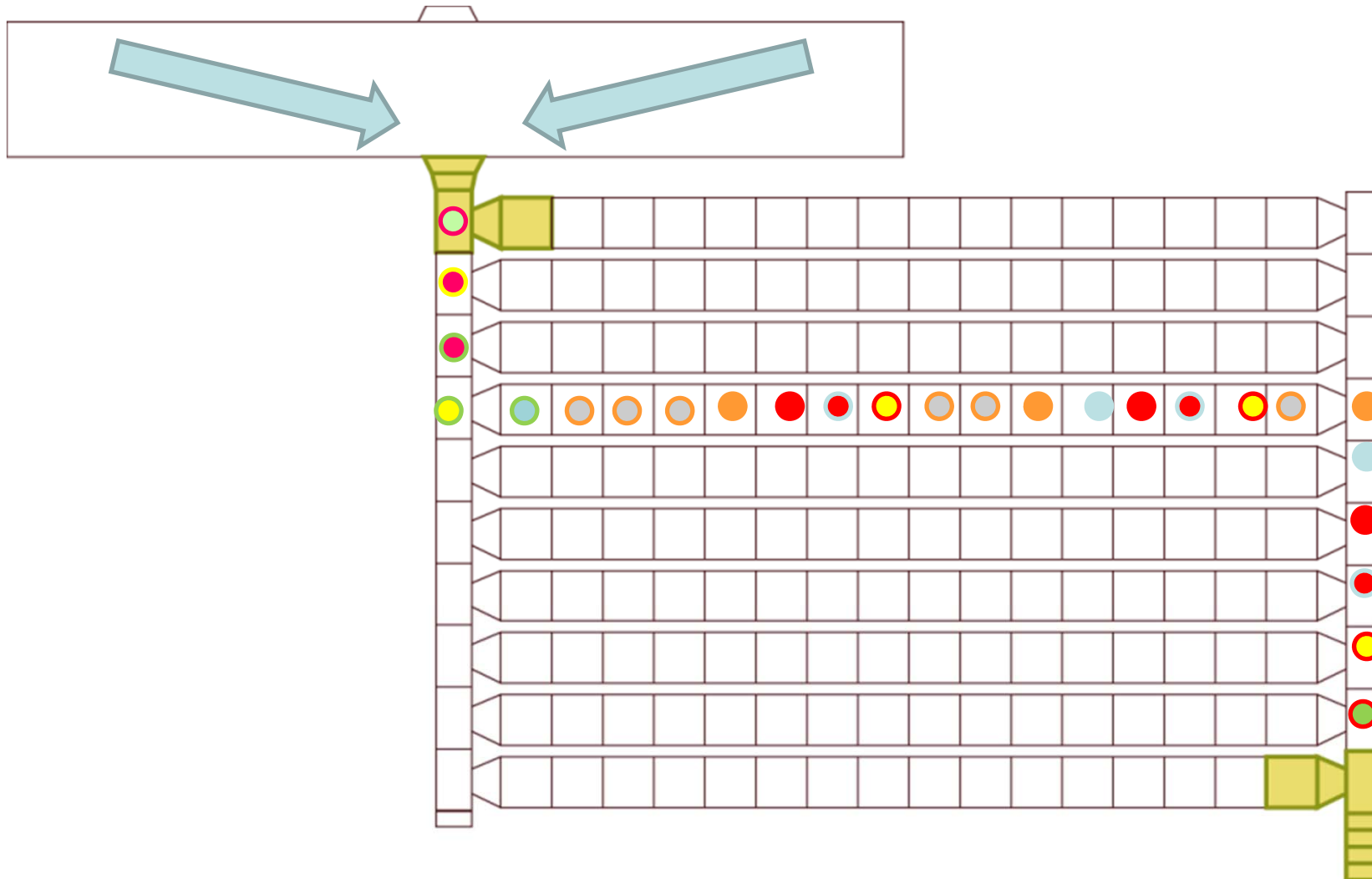
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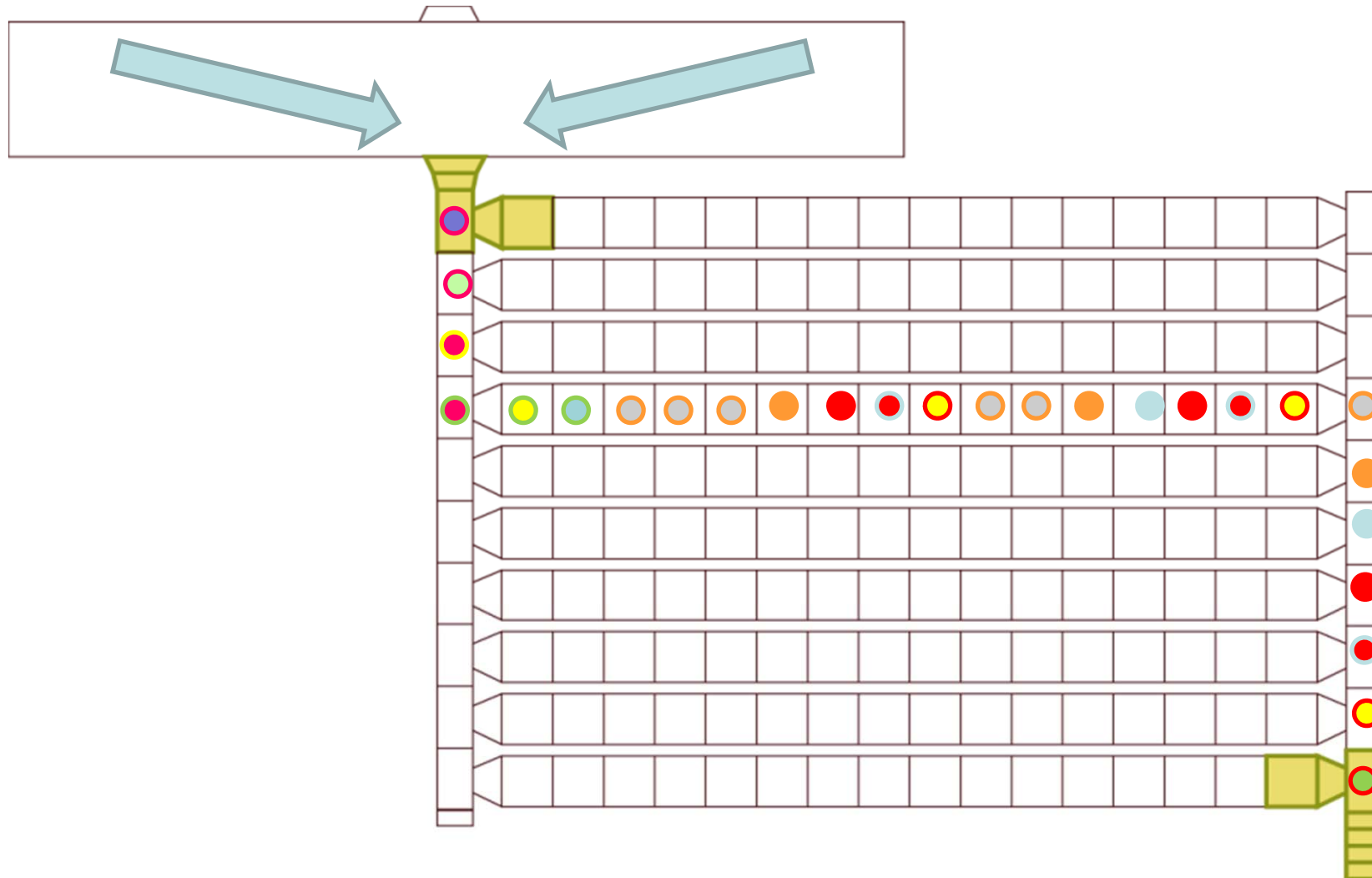


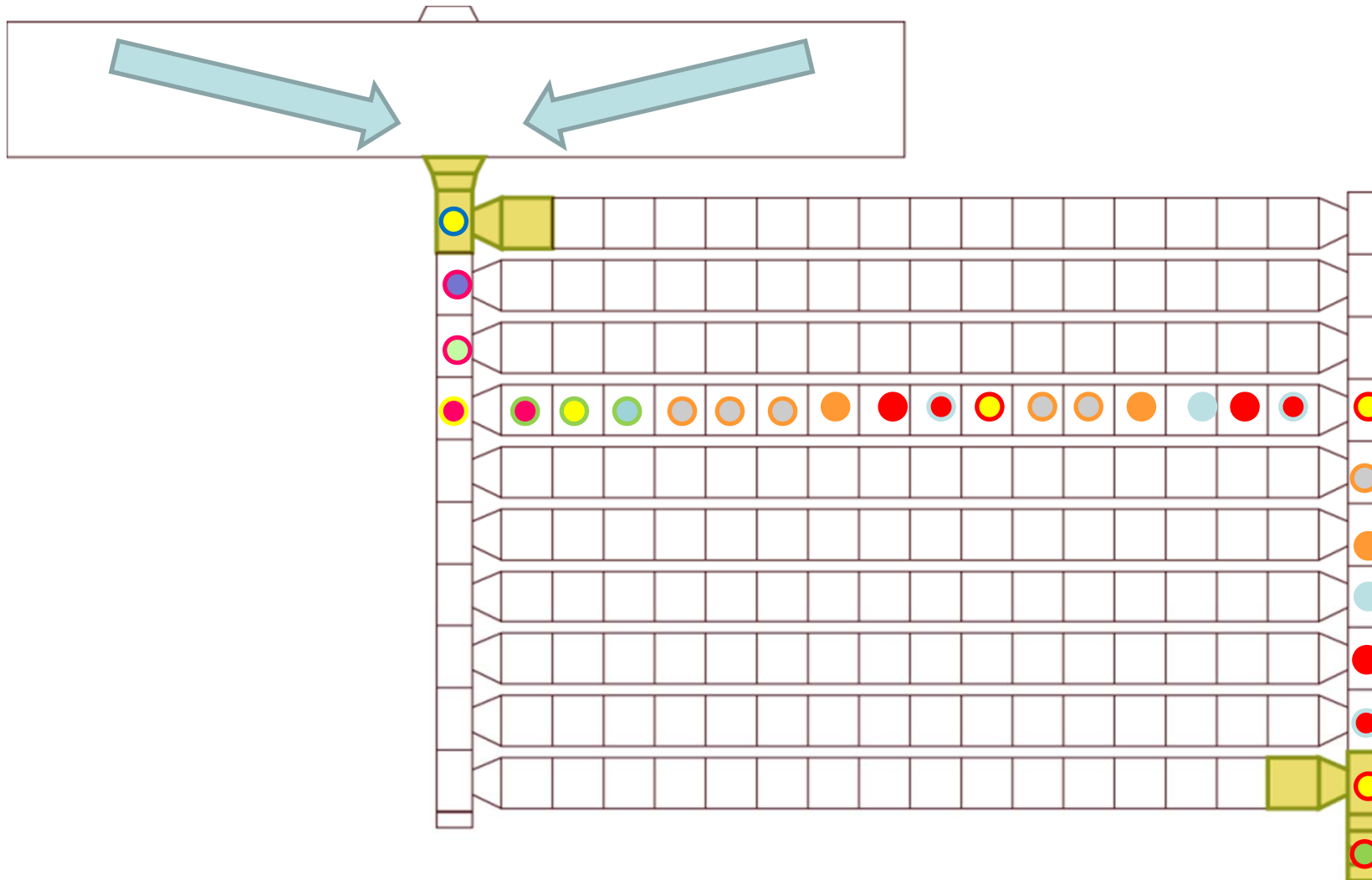
Continuous mode





Continuous mode

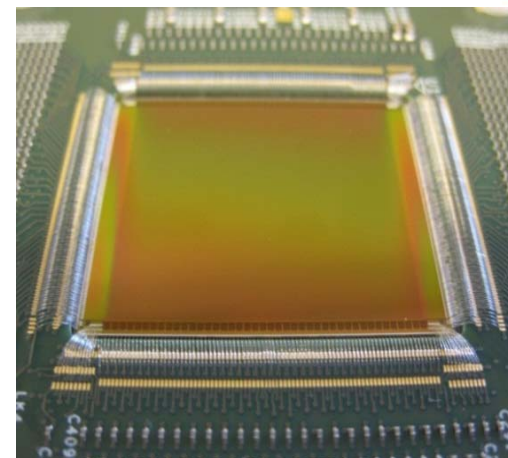






Performance summary

Parameter	Unit	Value
Pixel pitch (X)	um	30
Pixel pitch (Y)	um	30
Pixel format (X)		924
Pixel format (Y)		768
Number of pixels		709,632
Frame rate (burst mode)	fps	5,000,000
Frame rate (continuous mode)	fps	1,180
Pixel rate (burst mode)	Pixel/sec	1.42 T
Pixel rate (continuous mode)	Pixel/sec	0.84 G
Noise	e- rms	<10 e- rms
Full well capacity	e-	11,700
Camera gain	$\mu\text{V}/\text{e-}$	80
Dynamic range		>1,170
	dB	61.4
	bit	10.2
Fill Factor		11%
Quantum efficiency	Without microlens	2.3% (red) 2.2% (blue)





Imaging examples

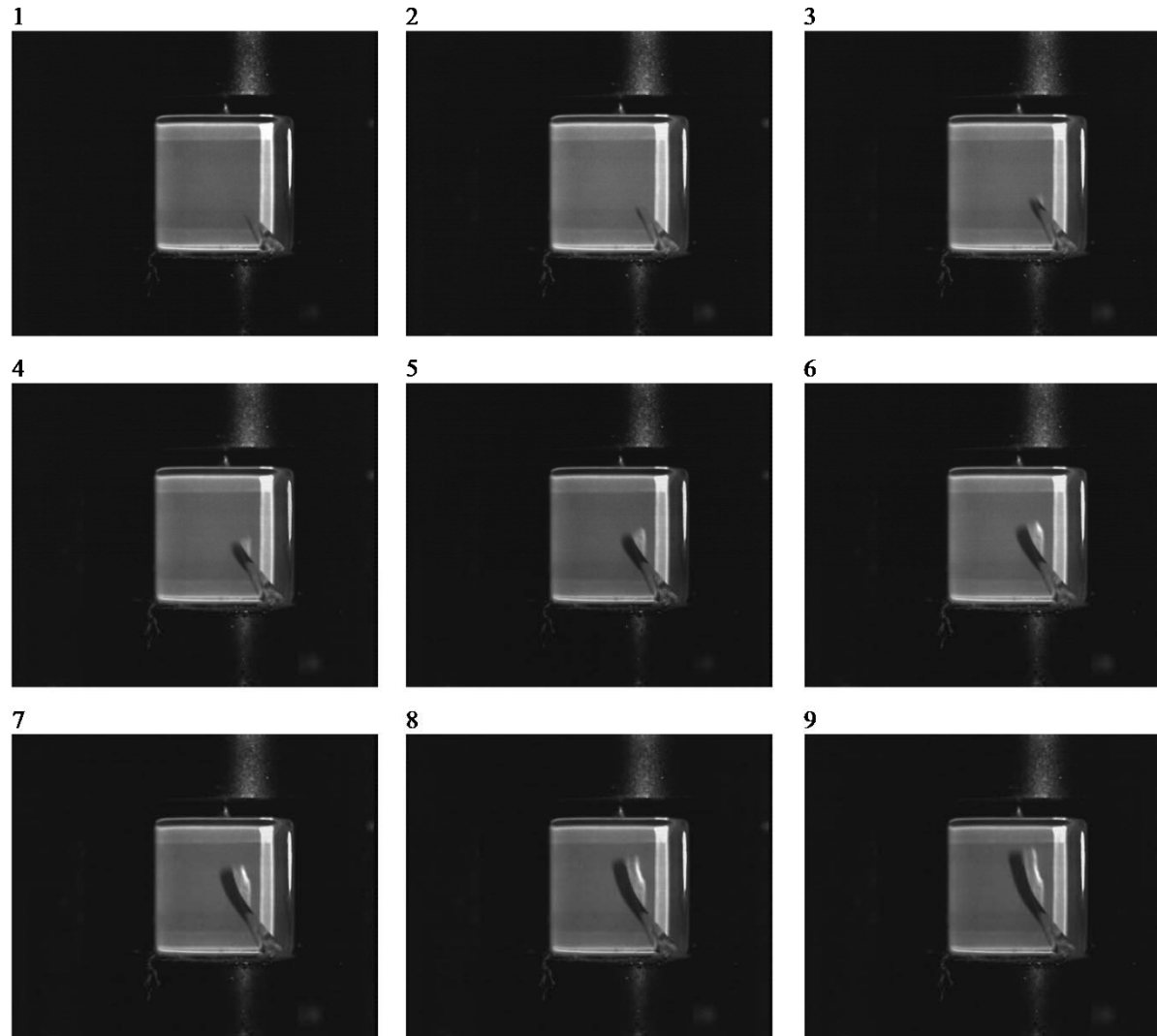


Figure 1: Consecutive images from a 1Mhz burst acquisition: Crack propagating through a glass tile at $\sim 1\text{km/sec}$



... and also sensors for: ESA miniaturised radiation monitor, particle physics, neutron detection, high-energy X-ray detection, SPAD ...

Demanding specifications from scientific instruments driving innovation → delivering to industry as well

Working to deliver optimal solutions: design, technology, post-processing, manufacturing, ...

‘Dreaming is mandatory’ (*H. Graasfma*, yesterday) ...

We can help you make your dreams reality
